

# Cinterion® PLS8-E

Hardware Interface Description

Version: 01.000a

Docld: PLS8-E\_HD\_v01.000a



Document Name: Cinterion® PLS8-E Hardware Interface Description

Version: **01.000a** 

Date: **2013-06-27** 

Docld: PLS8-E\_HD\_v01.000a

Status Confidential / Preliminary

#### **GENERAL NOTE**

THE USE OF THE PRODUCT INCLUDING THE SOFTWARE AND DOCUMENTATION (THE "PRODUCT") IS SUBJECT TO THE RELEASE NOTE PROVIDED TOGETHER WITH PRODUCT. IN ANY EVENT THE PROVISIONS OF THE RELEASE NOTE SHALL PREVAIL. THIS DOCUMENT CONTAINS INFORMATION ON GEMALTO M2M PRODUCTS. THE SPECIFICATIONS IN THIS DOCUMENT ARE SUBJECT TO CHANGE AT GEMALTO M2M'S DISCRETION. GEMALTO M2M GMBH GRANTS A NON-EXCLUSIVE RIGHT TO USE THE PRODUCT. THE RECIPIENT SHALL NOT TRANSFER, COPY, MODIFY, TRANSLATE, REVERSE ENGINEER, CREATE DERIVATIVE WORKS; DISASSEMBLE OR DECOMPILE THE PRODUCT OR OTHERWISE USE THE PRODUCT EXCEPT AS SPECIFICALLY AUTHORIZED. THE PRODUCT AND THIS DOCUMENT ARE PROVIDED ON AN "AS IS" BASIS ONLY AND MAY CONTAIN DEFICIENCIES OR INADEQUACIES. TO THE MAXIMUM EXTENT PERMITTED BY APPLICABLE LAW, GEMALTO M2M GMBH DISCLAIMS ALL WARRANTIES AND LIABILITIES. THE RECIPIENT UNDERTAKES FOR AN UNLIMITED PERIOD OF TIME TO OBSERVE SECRECY REGARDING ANY INFORMATION AND DATA PROVIDED TO HIM IN THE CONTEXT OF THE DELIVERY OF THE PRODUCT. THIS GENERAL NOTE SHALL BE GOVERNED AND CONSTRUED ACCORDING TO GERMAN LAW.

#### Copyright

Transmittal, reproduction, dissemination and/or editing of this document as well as utilization of its contents and communication thereof to others without express authorization are prohibited. Offenders will be held liable for payment of damages. All rights created by patent grant or registration of a utility model or design patent are reserved.

Copyright © 2013, Gemalto M2M GmbH, a Gemalto Company

#### **Trademark Notice**

Gemalto, the Gemalto logo, are trademarks and service marks of Gemalto and are registered in certain countries. Microsoft and Windows are either registered trademarks or trademarks of Microsoft Corporation in the United States and/or other countries. All other registered trademarks or trademarks mentioned in this document are property of their respective owners.

## **Contents**

0	Doc	ument H	istory		7		
1	Intro	duction			8		
	1.1	Suppo	rted Produ	ucts	8		
	1.2	Relate	d Docume	ents	8		
	1.3	Terms	and Abbr	eviations	8		
	1.4	Regula	atory and	Type Approval Information	11		
		1.4.1	Directive	es and Standards	11		
		1.4.2	SAR rec	quirements specific to portable mobiles	14		
		1.4.3	SELV R	equirements	15		
		1.4.4	Safety F	Precautions	15		
2	Prod	Product Concept					
	2.1	•					
	2.2	PLS8-	E System	Overview	18		
	2.3	Circuit	Concept		19		
3	Appl	ication I	nterface.		20		
	3.1	Opera	ting Mode	s	21		
	3.2	Power	Supply		22		
		3.2.1		ng Power Losses			
		3.2.2		ng Power Supply by AT Command			
	3.3		•	er-Down Scenarios			
		3.3.1		PLS8-E			
		3.3.2	_	states after Startup			
		3.3.3		PLS8-E Using AT Command			
		3.3.4		PLS8-E Using IGT Line			
		3.3.5		tic Shutdown			
			3.3.5.1	Thermal Shutdown			
			3.3.5.2	Undervoltage Shutdown			
			3.3.5.3	Overvoltage Shutdown			
		3.3.6		PLS8-E in Case of Emergency			
	3.4						
	3.5			Interface			
	0.0	3.5.1		ed ESD Protection for SIM Interface			
	3.6	Analog-to-Digital Converter (ADC)					
	3. <i>1</i> 3.8	3.7 GPIO Interface					
	3.0	3.8.1	•	ND Signal			
4	A 4			•			
4	4.1			Antenna Interface			
	4.1	4.1.1		Installation			
		4.1.1		Routing Design			
		4.1.2	4.1.2.1	Line Arrangement Examples			
			4.1.2.1 4.1.2.2				
			4.1.2.2	Routing Example	41		

5	Elec	trical, Re	eliability a	and Radio Characteristics	42
	5.1	Absolu	ute Maxim	um Ratings	42
	5.2	Opera	ting Temp	eratures	43
		5.2.1	Tempera	ature Allocation Model	43
	5.3	Storag	je Conditio	ons	44
	5.4	Reliab	ility Chara	cteristics	45
		5.4.1	Bending	Tests	45
	5.5	Pad As	ssignment	t and Signal Description	46
	5.6			atings	
	5.7	RF An	tenna Inte	rface Characteristics	55
	5.8	Electro	ostatic Dis	charge	57
6	Mecl	hanics, I	Mounting	and Packaging	58
	6.1	Mecha	anical Dim	ensions of PLS8-E	58
	6.2	Mount	ing PLS8-	E onto the Application Platform	60
		6.2.1	SMT PC	CB Assembly	60
			6.2.1.1	Land Pattern and Stencil	60
			6.2.1.2	Board Level Characterization	62
		6.2.2	Moisture	e Sensitivity Level	62
		6.2.3	Solderin	g Conditions and Temperature	63
			6.2.3.1	Reflow Profile	63
			6.2.3.2	Maximum Temperature and Duration	64
		6.2.4	Durabilit	ty and Mechanical Handling	
			6.2.4.1	Storage Life	
			6.2.4.2	Processing Life	
			6.2.4.3	Baking	
			6.2.4.4	Electrostatic Discharge	
	6.3	Packa	-		
	0.0	6.3.1	0 0	id Reel	
			6.3.1.1	Orientation	
			6.3.1.2	Barcode Label	
		6.3.2		Materials	
		0.0	6.3.2.1	Moisture Barrier Bag	
			6.3.2.2	Transportation Box	
7	Sam	nle Anni			
8				and the Time Anguerial	
	8.1			oment for Type Approval	
9	• •	Appendix			
	9.1			Accessories	
	92	Mounting Advice Sheet			76

## **Tables**

Table 1:	Directives	
Table 2:	Standards of European type approval	. 11
Table 3:	Requirements of quality	
Table 4:	Standards of the Ministry of Information Industry of the	
	People's Republic of China	. 13
Table 5:	Toxic or hazardous substances or elements with defined concentration	
	limits	. 13
Table 6:	Overview of operating modes	. 21
Table 7:	Signal states	
Table 8:	Temperature dependent behavior	. 28
Table 9:	Signals of the SIM interface (SMT application interface)	. 32
Table 10:	Return loss in the active band	. 37
Table 11:	Absolute maximum ratings	. 42
Table 12:	Board temperature	
Table 13:	Temperature allocation model	. 43
Table 14:	Storage conditions	
Table 15:	Summary of reliability test conditions	45
Table 16:	Overview: Pad assignments	. 47
Table 17:	Signal description	. 50
Table 18:	Voltage supply ratings	
Table 19:	Current consumption ratings	
Table 20:	RF Antenna interface GSM / UMTS/LTE (at operating temperature range)	. 55
Table 21:	Electrostatic values	
Table 22:	Reflow temperature ratings	
Table 23:	List of parts and accessories	. 74
Table 24:	Molex sales contacts (subject to change)	. 75
Table 25:	Hirose sales contacts (subject to change)	. 75

## **Figures**

Figure 1:	PLS8-E system overview	18
Figure 2:	PLS8-E block diagram	19
Figure 3:	Decoupling capacitor(s) for BATT+	22
Figure 4:	Power supply limits during transmit burst	
Figure 5:	Power-on with IGT	24
Figure 6:	Signal states during turn-off procedure	26
Figure 7:	Timing of IGT if used to switch off the module	27
Figure 8:	Shutdown by EMERG_OFF signal	30
Figure 9:	USB circuit	31
Figure 10:	UICC/SIM/USIM interface	33
Figure 11:	SIM interface - enhanced ESD protection	34
Figure 12:	PWR_IND signal	36
Figure 13:	Antenna pads (bottom view)	38
Figure 14:	Embedded Stripline line arrangement	39
Figure 15:	Micro-Stripline line arrangement samples	40
Figure 16:	Routing to application's RF connector	41
Figure 17:	PLS8-E evaluation board layer table	41
Figure 18:	Bending test setup	46
Figure 19:	PLS8-E bottom view: Pad assignments	48
Figure 20:	PLS8-E top view: Pad assignments	49
Figure 21:	PLS8-E – top and bottom view	58
Figure 22:	Dimensions of PLS8-E (all dimensions in mm)	59
Figure 23:	Land pattern (top layer)	
Figure 24:	Recommended design for 110 micron thick stencil (top layer)	61
Figure 25:	Recommended design for 150 micron thick stencil (top layer)	61
Figure 26:	Reflow Profile	63
Figure 27:	Carrier tape	66
Figure 28:	Roll direction	66
Figure 29:	Barcode label on tape reel	
Figure 30:	Moisture barrier bag (MBB) with imprint	68
Figure 31:	Moisture Sensitivity Label	69
Figure 32:	Humidity Indicator Card - HIC	70
Figure 33:	PLS8-E sample application	
Figure 34 <sup>.</sup>	Reference equipment for type approval	73

## 0 Document History

Preceding document: "PLS8-E Hardware Interface Description" Version 00.192 New document: "PLS8-E Hardware Interface Description" Version **01.000a** 

Chapter	What is new
	Removed LTE Bd1.
1.4.1	Revised versions of some standards and directives.
3.3.2	Revised some signal states mentioned in Table 7.
5.2	Revised section to include temperature allocation model for the module (incuding new Section 5.2.1 explaing this model).
5.6	Revised current consumption rating for POWER DOWN mode in Table 19.
2.2	Revised Figure 1 to include antenna detection.
3.3.2	Added note to Table 7 on internal pulls being implemented using JFETs.
3.4	Added note to Figure 9 recommending no blocking capacitors on VUSB line.
3.6	New section Analog-to-Digital Converter (ADC).
3.7	New section GPIO Interface.
5.4.1	New section Bending Tests.
5.5	Revised electrical characteristics for CCIN and VUSB_IN line
5.6	Revised and completed section giving power supply ratings.
5.7	Completed Table 20 listing RF antenna interface characteristics.

Preceding document: "PLS8-E Hardware Interface Description" Version 00.130 New document: "PLS8-E Hardware Interface Description" Version 00.192

Chapter	What is new
Throughout document	Removed SLEEP mode and references to power saving
3.3.1	Added maximum startup time for USB interface.
3.3.4	New section Turn off PLS8-E Using IGT Line.
3.3.6	Revised Figure 8 showing shutdown timings for EMERG_OFF signal.
3.4	Removed section "Power Saving".
3.4	Removed remarks on USB Suspended state and power saving.
5.5	Revised some electrical characteristics for SIM interface lines.
5.6	Added some more power supply ratings.
6.2.1.1	Revised Figure 24 and Figure 25.

New document: "PLS8-E Hardware Interface Description" Version 00.130

Chapter	What is new
	Initial document setup.

### 1 Introduction

The document<sup>1</sup> describes the hardware of the PLS8-E module, designed to connect to a cellular device application and the air interface. It helps you quickly retrieve interface specifications, electrical and mechanical details and information on the requirements to be considered for integrating further components.

## 1.1 Supported Products

This document applies to the following Cinterion products:

• Cinterion® PLS8-E module

### 1.2 Related Documents

- [1] AT Command Set for your Cinterion product
- [2] Release Notes for your Cinterion product
- [3] Application Note 48: SMT Module Integration

### 1.3 Terms and Abbreviations

Abbreviation	Description
ANSI	American National Standards Institute
ARP	Antenna Reference Point
CE	Conformité Européene (European Conformity)
CS	Coding Scheme
CS	Circuit Switched
CSD	Circuit Switched Data
DCS	Digital Cellular System
DL	Download
dnu	Do not use
DRX	Discontinuous Reception
DSB	Development Support Board
DTX	Discontinuous Transmission
EDGE	Enhanced Data rates for GSM Evolution
EGSM	Extended GSM
EMC	Electromagnetic Compatibility

<sup>1.</sup> The document is effective only if listed in the appropriate Release Notes as part of the technical documentation delivered with your Cinterion Wireless Modules product.

ESD Electrostatic Discharge ETS European Telecommunication Standard ETSI European Telecommunications Standards Institute FDD Frequency Division Duplex GPRS General Packet Radio Service GSM Global Standard for Mobile Communications HiZ High Impedance HSDPA High Speed Downlink Packet Access I/O Input/Output IMEI International Mobile Equipment Identity ISO International Standards Organization ITU International Telecommunications Union kbps kbits per second LED Light Emitting Diode LGA Land Grid Array LTE Long term evolution MBB Moisture barrier bag Mbps Mbits per second MIMO Multiple Input Multiple Output MLCC Multi Layer Ceramic Capacitor MO Mobile Originated MS Mobile Station, also referred to as TE MSL Moisture Sensitivity Level MT Mobile Terminated nc Not connected NTC Negative Temperature Coefficient PBCCH Packet Switched Broadcast Control Channel PCB Printed Circuit Board PCL Power Control Level PCS Personal Communication System, also referred to as GSM 1900 PD Pull Down resistor (appr. 100k) PSK Phase Shift Keying PU Pull Up resistor (appr. 100k)	Abbreviation	Description
ETSI European Telecommunications Standards Institute  FDD Frequency Division Duplex  GPRS General Packet Radio Service  GSM Global Standard for Mobile Communications  HiZ High Impedance  HSDPA High Speed Downlink Packet Access  I/O Input/Output  IMEI International Mobile Equipment Identity  ISO International Telecommunications Union  kbps kbits per second  LED Light Emitting Diode  LGA Land Grid Array  LTE Long term evolution  MBB Moisture barrier bag  Mbps Mbits per second  MCS Modulation and Coding Scheme  MIMO Multiple Input Multiple Output  MLCC Multi Layer Ceramic Capacitor  MO Mobile Originated  MS Mobile Station, also referred to as TE  MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	ESD	Electrostatic Discharge
FDD Frequency Division Duplex GPRS General Packet Radio Service GSM Global Standard for Mobile Communications HiZ High Impedance HSDPA High Speed Downlink Packet Access I/O Input/Output IMEI International Mobile Equipment Identity ISO International Standards Organization ITU International Telecommunications Union kbps kbits per second LED Light Emitting Diode LGA Land Grid Array LTE Long term evolution MBB Moisture barrier bag Mbps Mbits per second MCS Modulation and Coding Scheme MIMO Multiple Input Multiple Output MLCC Multi Layer Ceramic Capacitor M/O Mobile Originated M/S Mobile Station, also referred to as TE MSL Moisture Sensitivity Level MT Mobile Terminated nc Not connected NTC Negative Temperature Coefficient PBCCH Packet Switched Broadcast Control Channel PCB Printed Circuit Board PCL Power Control Level PCS Personal Communication System, also referred to as GSM 1900 PDU Protocol Data Unit PS Packet Switched PSK Phase Shift Keying	ETS	European Telecommunication Standard
GPRS General Packet Radio Service GSM Global Standard for Mobile Communications HiZ High Impedance HSDPA High Speed Downlink Packet Access I/O Input/Output IMEI International Mobile Equipment Identity ISO International Standards Organization ITU International Telecommunications Union kbps kbits per second LED Light Emitting Diode LGA Land Grid Array LTE Long term evolution MBB Moisture barrier bag Mbps Mbits per second MCS Modulation and Coding Scheme MIMO Multiple Input Multiple Output MLCC Multi Layer Ceramic Capacitor MO Mobile Originated MS Mobile Station, also referred to as TE MSL Moisture Sensitivity Level MT Mobile Terminated nc Not connected NTC Negative Temperature Coefficient PBCCH Packet Switched Broadcast Control Channel PCB Printed Circuit Board PCL Power Control Level PCS Personal Communication System, also referred to as GSM 1900 PDU Protocol Data Unit PS Packet Switched PSK Phase Shift Keying	ETSI	European Telecommunications Standards Institute
GSM Global Standard for Mobile Communications HiZ High Impedance HSDPA High Speed Downlink Packet Access I/O Input/Output IMEI International Mobile Equipment Identity ISO International Standards Organization ITU International Telecommunications Union kbps kbits per second LED Light Emitting Diode LGA Land Grid Array LTE Long term evolution MBB Moisture barrier bag Mbps Mbits per second MCS Modulation and Coding Scheme MIMO Multiple Input Multiple Output MLCC Multi Layer Ceramic Capacitor MO Mobile Originated MS Moisture Sensitivity Level MT Mobile Terminated nc Not connected NTC Negative Temperature Coefficient PBCCH Packet Switched Broadcast Control Channel PCB Printed Circuit Board PCL Power Control Level PCS Personal Communication System, also referred to as GSM 1900 PD Pull Down resistor (appr. 100k) PDU Protocol Data Unit PS Packet Switched PSK Phase Shift Keying	FDD	Frequency Division Duplex
HiZ High Impedance HSDPA High Speed Downlink Packet Access I/O Input/Output IMEI International Mobile Equipment Identity ISO International Standards Organization ITU International Telecommunications Union kbps kbits per second LED Light Emitting Diode LGA Land Grid Array LTE Long term evolution MBB Moisture barrier bag Mbps Mbits per second MCS Modulation and Coding Scheme MIMO Multiple Input Multiple Output MLCC Multi Layer Ceramic Capacitor MO Mobile Originated MS Moisture Sensitivity Level MT Mobile Terminated nc Not connected NTC Negative Temperature Coefficient PBCCH Packet Switched Broadcast Control Channel PCB Printed Circuit Board PCL Power Control Level PCS Personal Communication System, also referred to as GSM 1900 PD Pull Down resistor (appr. 100k) PDU Protocol Data Unit PS Packet Switched PSK Phase Shift Keying	GPRS	General Packet Radio Service
HSDPA High Speed Downlink Packet Access  I/O Input/Cutput  IMEI International Mobile Equipment Identity  ISO International Standards Organization  ITU International Telecommunications Union  kbps kbits per second  LED Light Emitting Diode  LGA Land Grid Array  LTE Long term evolution  MBB Moisture barrier bag  Mbps Mbits per second  MCS Modulation and Coding Scheme  MIMO Multiple Input Multiple Output  MLCC Multi Layer Ceramic Capacitor  MO Mobile Originated  MS Mobile Station, also referred to as TE  MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PSK Phase Shift Keying	GSM	Global Standard for Mobile Communications
I/O Input/Output  IMEI International Mobile Equipment Identity  ISO International Standards Organization  ITU International Telecommunications Union  kbps kbits per second  LED Light Emitting Diode  LGA Land Grid Array  LTE Long term evolution  MBB Moisture barrier bag  Mbps Mbits per second  MCS Modulation and Coding Scheme  MIMO Multiple Input Multiple Output  MLCC Multi Layer Ceramic Capacitor  MO Mobile Originated  MS Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PSK Phase Shift Keying	HiZ	High Impedance
IMEI International Mobile Equipment Identity ISO International Standards Organization ITU International Telecommunications Union Ikbps Ikbits per second LED Light Emitting Diode LGA Land Grid Array LTE Long term evolution IMBB Moisture barrier bag IMBB Moisture Second IMBB Moisture Second IMBB Moisture Sensitivity Capacitor IMBB Mobile Originated IMBC Multiple Input Multiple Output IMBCC Multi Layer Ceramic Capacitor IMBC Mobile Originated IMBC Mobile Station, also referred to as TE IMBL Moisture Sensitivity Level IMT Mobile Terminated INC Negative Temperature Coefficient INTC Negative Temperature Coefficient INTC Negative Temperature Coefficient INTC PECCH Packet Switched Broadcast Control Channel INTC PCB Printed Circuit Board INTO PCC Personal Communication System, also referred to as GSM 1900 INTO PD Pull Down resistor (appr. 100k) INTO PCC Packet Switched INTO PACKET SWITCHED	HSDPA	High Speed Downlink Packet Access
International Standards Organization ITU International Telecommunications Union kbps kbits per second LED Light Emitting Diode LGA Land Grid Array LTE Long term evolution MBB Moisture barrier bag Mbps Mbits per second MCS Modulation and Coding Scheme MIMO Multiple Input Multiple Output MLCC Multi Layer Ceramic Capacitor MO Mobile Originated MS Mobile Station, also referred to as TE MSL Moisture Sensitivity Level MT Mobile Terminated nc Not connected NTC Negative Temperature Coefficient PBCCH Packet Switched Broadcast Control Channel PCB Printed Circuit Board PCL Power Control Level PCS Personal Communication System, also referred to as GSM 1900 PD Pull Down resistor (appr. 100k) PDU Protocol Data Unit PS Packet Switched PSK Phase Shift Keying	I/O	Input/Output
ITU International Telecommunications Union  kbps kbits per second  LED Light Emitting Diode  LGA Land Grid Array  LTE Long term evolution  MBB Moisture barrier bag  Mbps Mbits per second  MCS Modulation and Coding Scheme  MIMO Multiple Input Multiple Output  MLCC Multi Layer Ceramic Capacitor  MO Mobile Originated  MS Mobile Station, also referred to as TE  MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	IMEI	International Mobile Equipment Identity
kbps       kbits per second         LED       Light Emitting Diode         LGA       Land Grid Array         LTE       Long term evolution         MBB       Moisture barrier bag         Mbps       Mbits per second         MCS       Modulation and Coding Scheme         MIMO       Multiple Input Multiple Output         MLCC       Multi Layer Ceramic Capacitor         MO       Mobile Originated         MS       Mobile Station, also referred to as TE         MSL       Moisture Sensitivity Level         MT       Mobile Terminated         nc       Not connected         NTC       Negative Temperature Coefficient         PBCCH       Packet Switched Broadcast Control Channel         PCB       Printed Circuit Board         PCL       Power Control Level         PCS       Personal Communication System, also referred to as GSM 1900         PD       Pull Down resistor (appr. 100k)         PDU       Protocol Data Unit         PS       Packet Switched         PSK       Phase Shift Keying	ISO	International Standards Organization
LED Light Emitting Diode  LGA Land Grid Array  LTE Long term evolution  MBB Moisture barrier bag  Mbps Mbits per second  MCS Modulation and Coding Scheme  MIMO Multiple Input Multiple Output  MLCC Multi Layer Ceramic Capacitor  MO Mobile Originated  MS Mobile Station, also referred to as TE  MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	ITU	International Telecommunications Union
LGA Land Grid Array  LTE Long term evolution  MBB Moisture barrier bag  Mbps Mbits per second  MCS Modulation and Coding Scheme  MIMO Multiple Input Multiple Output  MLCC Multi Layer Ceramic Capacitor  MO Mobile Originated  MS Mobile Station, also referred to as TE  MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	kbps	kbits per second
LTE Long term evolution  MBB Moisture barrier bag  Mbps Mbits per second  MCS Modulation and Coding Scheme  MIMO Multiple Input Multiple Output  MLCC Multi Layer Ceramic Capacitor  MO Mobile Originated  MS Mobile Station, also referred to as TE  MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	LED	Light Emitting Diode
MBB Moisture barrier bag  Mbps Mbits per second  MCS Modulation and Coding Scheme  MIMO Multiple Input Multiple Output  MLCC Multi Layer Ceramic Capacitor  MO Mobile Originated  MS Mobile Station, also referred to as TE  MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	LGA	Land Grid Array
Mbps Mbits per second  MCS Modulation and Coding Scheme  MIMO Multiple Input Multiple Output  MLCC Multi Layer Ceramic Capacitor  MO Mobile Originated  MS Mobile Station, also referred to as TE  MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	LTE	Long term evolution
MCS Modulation and Coding Scheme  MIMO Multiple Input Multiple Output  MLCC Multi Layer Ceramic Capacitor  MO Mobile Originated  MS Mobile Station, also referred to as TE  MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	MBB	Moisture barrier bag
MIMO Multiple Input Multiple Output  MLCC Multi Layer Ceramic Capacitor  MO Mobile Originated  MS Mobile Station, also referred to as TE  MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	Mbps	Mbits per second
MLCC Multi Layer Ceramic Capacitor  MO Mobile Originated  MS Mobile Station, also referred to as TE  MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	MCS	Modulation and Coding Scheme
MO Mobile Originated  MS Mobile Station, also referred to as TE  MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	MIMO	Multiple Input Multiple Output
MS Mobile Station, also referred to as TE  MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	MLCC	Multi Layer Ceramic Capacitor
MSL Moisture Sensitivity Level  MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	MO	Mobile Originated
MT Mobile Terminated  nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	MS	Mobile Station, also referred to as TE
nc Not connected  NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	MSL	Moisture Sensitivity Level
NTC Negative Temperature Coefficient  PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	MT	Mobile Terminated
PBCCH Packet Switched Broadcast Control Channel  PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	nc	Not connected
PCB Printed Circuit Board  PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	NTC	Negative Temperature Coefficient
PCL Power Control Level  PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	PBCCH	Packet Switched Broadcast Control Channel
PCS Personal Communication System, also referred to as GSM 1900  PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	PCB	Printed Circuit Board
PD Pull Down resistor (appr. 100k)  PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	PCL	Power Control Level
PDU Protocol Data Unit  PS Packet Switched  PSK Phase Shift Keying	PCS	Personal Communication System, also referred to as GSM 1900
PS Packet Switched PSK Phase Shift Keying	PD	Pull Down resistor (appr. 100k)
PSK Phase Shift Keying	PDU	Protocol Data Unit
, ,	PS	Packet Switched
PU Pull Up resistor (appr. 100k)	PSK	Phase Shift Keying
	PU	Pull Up resistor (appr. 100k)

Abbreviation	Description
QAM	Quadrature Amplitude Modulation
R&TTE	Radio and Telecommunication Terminal Equipment
RF	Radio Frequency
rfu	Reserved for future use
RTC	Real Time Clock
Rx	Receive Direction
SAR	Specific Absorption Rate
SELV	Safety Extra Low Voltage
SIM	Subscriber Identification Module
SMD	Surface Mount Device
SMS	Short Message Service
SMT	Surface Mount Technology
SRAM	Static Random Access Memory
SRB	Signalling Radio Bearer
TE	Terminal Equipment
TPC	Transmit Power Control
TS	Technical Specification
Tx	Transmit Direction
UL	Upload
UMTS	Universal Mobile Telecommunications System
URC	Unsolicited Result Code
USB	Universal Serial Bus
UICC	USIM Integrated Circuit Card
USIM	UMTS Subscriber Identification Module
WCDMA	Wideband Code Division Multiple Access

## 1.4 Regulatory and Type Approval Information

### 1.4.1 Directives and Standards

PLS8-E has been designed to comply with the directives and standards listed below.

It is the responsibility of the application manufacturer to ensure compliance of the final product with all provisions of the applicable directives and standards as well as with the technical specifications provided in the "PLS8-E Hardware Interface Description".

Table 1: Directives

99/05/EC	Directive of the European Parliament and of the council of 9 March 1999 on radio equipment and telecommunications terminal equipment and the mutual recognition of their conformity (in short referred to as R&TTE Directive 1999/5/EC).  The product is labeled with the CE conformity mark
ECE-R 10	Economic Commission for Europe (ECE) Regulation No. 10: Uniform provisions concerning the approval of vehicles with regard to electromagnetic compatibility
2002/95/EC (RoHS 1) 2011/65/EC (RoHS 2)	Directive of the European Parliament and of the Council of 27 January 2003 (and revised on 8 June 2011) on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS)

**Table 2:** Standards of European type approval

3GPP TS 51.010-1	Digital cellular telecommunications system (Release 7); Mobile Station (MS) conformance specification;
ETSI EN 301 511 V9.0.2	Global System for Mobile communications (GSM); Harmonized standard for mobile stations in the GSM 900 and DCS 1800 bands covering essential requirements under article 3.2 of the R&TTE directive (1999/5/EC)
GCF-CC V3.48	Global Certification Forum - Certification Criteria
ETSI EN 301 489-01 V1.9.1	Electromagnetic Compatibility and Radio spectrum Matters (ERM); Electromagnetic Compatibility (EMC) standard for radio equipment and services; Part 1: Common Technical Requirements
ETSI EN 301 489-07 V1.3.1	Electromagnetic Compatibility and Radio spectrum Matters (ERM); Electromagnetic Compatibility (EMC) standard for radio equipment and services; Part 7: Specific conditions for mobile and portable radio and ancillary equipment of digital cellular radio telecommunications systems (GSM and DCS)
ETSI EN 301 489-24 V1.5.1	Electromagnetic Compatibility and Radio spectrum Matters (ERM); Electromagnetic Compatibility (EMC) standard for radio equipment and services; Part 24: Specific conditions for IMT-2000 CDMA Direct Spread (UTRA) for Mobile and portable (UE) radio and ancillary equipment
EN 301 908-01 V5.2.1	Electromagnetic compatibility and Radio spectrum Matters (ERM); Base Stations (BS) and User Equipment (UE) for IMT-2000 Third Generation cellular networks; Part 1: Harmonized EN for IMT-2000, introduction and common requirements of article 3.2 of the R&TTE Directive

1.4 Regulatory and Type Approval Information

Table 2: Standards of European type approval

EN 301 908-02 V5.2.1	Electromagnetic compatibility and Radio spectrum Matters (ERM); Base Stations (BS) and User Equipment (UE) for IMT-2000 Third Generation cellular networks; Part 2: Harmonized EN for IMT-2000, CDMA Direct Spread (UTRA FDD) (UE) covering essential requirements of article 3.2 of the R&TTE Directive
EN 301 908-13 V5.2.1	IMT cellular networks; Harmonized EN covering the essential requirements of article 3.2 of the R&TTE Directive; Part 13: Evolved Universal Terrestrial Radio Access (E-UTRA) User Equipment (UE)
EN 300 440-02 V1.3.1	Electromagnetic compatibility and Radio spectrum Matters (ERM); Short range devices; Radio equipment to be used in the 1 GHz to 40 GHz frequency range; Part 2: Harmonized EN covering essential requirements of article 3.2 of the R&TTE Directive
EN 62311:2008	Assessment of electronic and electrical equipment related to human exposure restrictions for electromagnetic fields (0 Hz - 300 GHz)
IEC/EN 60950-1:2006+ A11:2009+A1:2010+ A12:2011	Safety of information technology equipment

### Table 3: Requirements of quality

IEC 60068	Environmental testing
DIN EN 60529	IP codes

Table 4: Standards of the Ministry of Information Industry of the People's Republic of China

SJ/T 11363-2006	"Requirements for Concentration Limits for Certain Hazardous Substances in Electronic Information Products" (2006-06).
SJ/T 11364-2006	"Marking for Control of Pollution Caused by Electronic Information Products" (2006-06).  According to the "Chinese Administration on the Control of Pollution caused by Electronic Information Products" (ACPEIP) the EPUP, i.e., Environmental Protection Use Period, of this product is 20 years as per the symbol shown here, unless otherwise marked. The EPUP is valid only as long as the product is operated within the operating limits described in the Cinterion Hardware Interface Description.  Please see Table 5 for an overview of toxic or hazardous substances or elements that might be contained in product parts in concentrations above the limits defined by SJ/T 11363-2006.

Table 5: Toxic or hazardous substances or elements with defined concentration limits

部件名称	有毒有害物质或元素 Hazardous substances					
Name of the part	铅 (Pb)	汞 (Hg)	镉 (Cd)	六价铬 (Cr(VI))	多溴联苯 (PBB)	多溴二苯醚 (PBDE)
金属部件 (Metal Parts)	0	0	0	0	0	0
电路模块 (Circuit Modules)	х	0	0	0	0	0
电缆及电缆组件 (Cables and Cable Assemblies)	0	0	0	0	0	0
塑料和聚合物部件 (Plastic and Polymeric parts)	0	0	0	0	0	0

#### 0:

表示该有毒有害物质在该部件所有均质材料中的含量均在SJ/T11363-2006 标准规定的限量要求以下。 Indicates that this toxic or hazardous substance contained in all of the homogeneous materials for this part is below the limit requirement in SJ/T11363-2006.

#### x.

表示该有毒有害物质至少在该部件的某一均质材料中的含量超出SJ/T11363-2006标准规定的限量要求。 Indicates that this toxic or hazardous substance contained in at least one of the homogeneous materials used for this part *might exceed* the limit requirement in SJ/T11363-2006.

### 1.4.2 SAR requirements specific to portable mobiles

Mobile phones, PDAs or other portable transmitters and receivers incorporating a GSM module must be in accordance with the guidelines for human exposure to radio frequency energy. This requires the Specific Absorption Rate (SAR) of portable PLS8-E based applications to be evaluated and approved for compliance with national and/or international regulations.

Since the SAR value varies significantly with the individual product design manufacturers are advised to submit their product for approval if designed for portable use. For European markets the relevant directives are mentioned below. It is the responsibility of the manufacturer of the final product to verify whether or not further standards, recommendations or directives are in force outside these areas.

Products intended for sale on European markets

EN 50360

Product standard to demonstrate the compliance of mobile phones with the basic restrictions related to human exposure to electromagnetic fields (300MHz - 3GHz)

### 1.4.3 **SELV** Requirements

The power supply connected to the PLS8-E module shall be in compliance with the SELV requirements defined in EN 60950-1.

## 1.4.4 Safety Precautions

The following safety precautions must be observed during all phases of the operation, usage, service or repair of any cellular terminal or mobile incorporating PLS8-E. Manufacturers of the cellular terminal are advised to convey the following safety information to users and operating personnel and to incorporate these guidelines into all manuals supplied with the product. Failure to comply with these precautions violates safety standards of design, manufacture and intended use of the product. Cinterion Wireless Modules assumes no liability for customer's failure to comply with these precautions.



When in a hospital or other health care facility, observe the restrictions on the use of mobiles. Switch the cellular terminal or mobile off, if instructed to do so by the guidelines posted in sensitive areas. Medical equipment may be sensitive to RF energy.

The operation of cardiac pacemakers, other implanted medical equipment and hearing aids can be affected by interference from cellular terminals or mobiles placed close to the device. If in doubt about potential danger, contact the physician or the manufacturer of the device to verify that the equipment is properly shielded. Pacemaker patients are advised to keep their hand-held mobile away from the pacemaker, while it is on.



Switch off the cellular terminal or mobile before boarding an aircraft. Make sure it cannot be switched on inadvertently. The operation of wireless appliances in an aircraft is forbidden to prevent interference with communications systems. Failure to observe these instructions may lead to the suspension or denial of cellular services to the offender, legal action, or both.



Do not operate the cellular terminal or mobile in the presence of flammable gases or fumes. Switch off the cellular terminal when you are near petrol stations, fuel depots, chemical plants or where blasting operations are in progress. Operation of any electrical equipment in potentially explosive atmospheres can constitute a safety hazard.



Your cellular terminal or mobile receives and transmits radio frequency energy while switched on. Remember that interference can occur if it is used close to TV sets, radios, computers or inadequately shielded equipment. Follow any special regulations and always switch off the cellular terminal or mobile wherever forbidden, or when you suspect that it may cause interference or danger.



#### **IMPORTANT!**

Cellular terminals or mobiles operate using radio signals and cellular networks. Because of this, connection cannot be guaranteed at all times under all conditions. Therefore, you should never rely solely upon any wireless device for essential communications, for example emergency calls.

Remember, in order to make or receive calls, the cellular terminal or mobile must be switched on and in a service area with adequate cellular signal strength.

Some networks do not allow for emergency calls if certain network services or phone features are in use (e.g. lock functions, fixed dialing etc.). You may need to deactivate those features before you can make an emergency call.

Some networks require that a valid SIM card be properly inserted in the cellular terminal or mobile.

## 2 Product Concept

## 2.1 Key Features at a Glance

Feature	Implementation		
General			
Frequency bands	GSM/GPRS/EDGE: Dual band, 900/1800MHz UMTS/HSPA+: Triple band, 900 (BdVIII) / 1800 (BdIII) / 2100MHz (Bd LTE: band, 800 (Bd20) / 900 (Bd8) / 1800 (Bd3) / 2600MHz (Bd7)		
GSM class	Small MS		
Output power (according to Release 99)	Class 4 (+33dBm ±2dB) for EGSM900 Class 1 (+30dBm ±2dB) for GSM1800 Class E2 (+27dBm ± 3dB) for GSM 900 8-PSK Class E2 (+26dBm +3 /-4dB) for GSM 1800 8-PSK Class 3 (+24dBm +1/-3dB) for UMTS 2100, WCDMA FDD Bdl Class 3 (+24dBm +1/-3dB) for UMTS 1800, WCDMA FDD BdIII Class 3 (+24dBm +1/-3dB) for UMTS 900, WCDMA FDD BdVIII		
Output power (according to Release 8)	Class 3 (+23dBm +-2dB) for LTE 2600, LTE FDD Bd7 Class 3 (+23dBm +-2dB) for LTE 1800, LTE FDD Bd3 Class 3 (+23dBm +-2dB) for LTE 900, LTE FDD Bd8 Class 3 (+23dBm +-2dB) for LTE 800, LTE FDD Bd20		
Power supply	$3.3V \le V_{BATT+} \le 4.2V$		
Operating temperature (board temperature)	Normal operation: -30°C to +85°C Extended operation: -40°C to +95°C		
Physical	Dimensions: 33mm x 29mm x 2.2mm Weight: approx. 4.5g		
RoHS	All hardware components fully compliant with EU RoHS Directive		
LTE features			
3GPP Release 9	UE CAT 3 supported DL 100Mbps, UL 50Mbps 2x2 MIMO in DL direction		
HSPA features			
3GPP Release 8	UE CAT. 1-14, 16, 24 supported DC-HSPA+ – DL 42Mbps; 2x2 MIMO – DL 28.8Mbps HSUPA – UL 5.76Mbps Compressed mode (CM) supported according to 3GPP TS25.212		
UMTS features			
3GPP Release 8	PS data rate – 384 kbps DL / 384 kbps UL		

Feature	Implementation		
GSM / GPRS / EGPRS f	eatures		
Data transfer	GPRS:  • Multislot Class 12  • Mobile Station Class B  • Coding Scheme 1 – 4  EGPRS:  • Multislot Class 12  • EDGE E2 power class for 8 PSK  • Downlink coding schemes – CS 1-4, MCS 1-9  • Uplink coding schemes – CS 1-4, MCS 1-9  • SRB loopback and test mode B  • 8-bit, 11-bit RACH  • 1 phase/2 phase access procedures  • Link adaptation and IR  • NACC, extended UL TBF  • Mobile Station Class B		
Software			
AT commands	Hayes, 3GPP TS 27.007 and 27.005, and proprietary Cinterion Wireless Modules commands		
Firmware update	Generic update from host application over USB		
Interfaces			
Module interface	Surface mount device with solderable connection pads (SMT application interface). Land grid array (LGA) technology ensures high solder joint reliability and provides the possibility to use an optional module mounting socket. For more information on how to integrate SMT modules see also [3]. This application note comprises chapters on module mounting and application layout issues as well as on additional SMT application development equipment.		
Antenna	50Ohms. GSM/UMTS/LTE main antenna, UMTS/LTE Diversity/MIMO antenna		
USB	USB 2.0 High Speed (480Mbit/s) device interface, Full Speed (12Mbit/s) compliant		
UICC interface	Supported chip cards: UICC/SIM/USIM 3V, 1.8V		
Power on/off, Reset			
Power on/off	Switch-on by hardware signal IGT Switch-off by AT command (AT^SMSO) or IGT Automatic switch-off in case of critical temperature or voltage conditions		
Reset	Orderly shutdown and reset by AT command		
Emergency-off	Emergency-off by hardware signal EMERG_OFF if IGT is not active		
Special Features			
Antenna	SAIC (Single Antenna Interference Cancellation) / DARP (Downlink Advanced Receiver Performance) Rx Diversity (receiver type 3i - 64-QAM) / MIMO		

Feature	Implementation
Evaluation kit	
Evaluation module	PLS8-E module soldered onto a dedicated PCB that can be connected to an adapter in order to be mounted onto the DSB75.
DSB75	DSB75 Development Support Board designed to test and type approve Cinterion Wireless Modules and provide a sample configuration for application engineering. A special adapter is required to connect the PLS8-E evaluation module to the DSB75.

## 2.2 PLS8-E System Overview

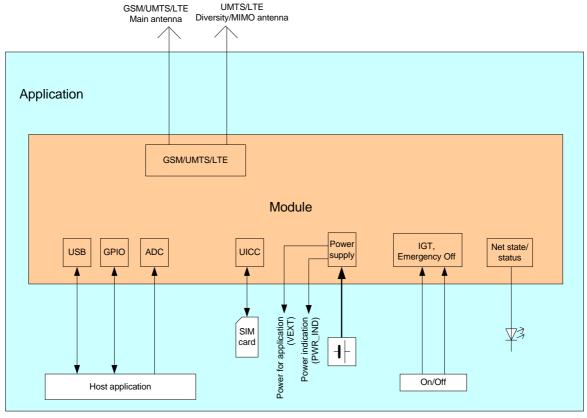


Figure 1: PLS8-E system overview

## 2.3 Circuit Concept

Figure 2 shows a block diagram of the PLS8-E module and illustrates the major functional components:

#### Baseband block:

- GSM/UMTS controller/transceiver/power supply
- Stacked Flash/RAM memory with multiplexed address data bus
- Application interface (SMT with connecting pads)

#### RF section:

- RF transceiver
- · RF power amplifier/frontend
- RF filter
- Antenna pad

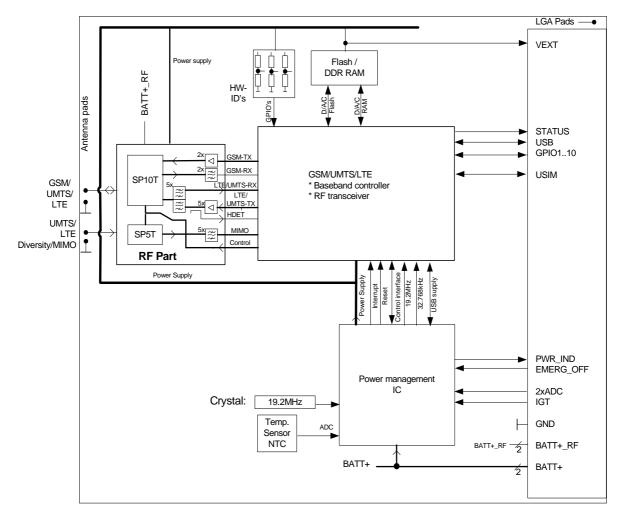


Figure 2: PLS8-E block diagram

## 3 Application Interface

PLS8-E is equipped with an SMT application interface (LGA pads) that connects to the external application. The host interface incorporates several sub-interfaces described in the following sections:

- Operating modes see Section 3.1
- Power supply see Section 3.2
- USB interface see Section 3.4
- UICC/SIM/USIM interface see Section 3.5
- ADC interface Section 3.6
- GPIO interface Section 3.7
- Control line: PWR\_IND see Section 3.8

## 3.1 Operating Modes

The table below briefly summarizes the various operating modes referred to in the following chapters.

Table 6: Overview of operating modes

Mode	Function		
Normal operation	GSM / GPRS / UMTS / HSPA / LTE IDLE	No data transfer in progress.	
	GPRS DATA	GPRS data transfer in progress. Power consumption depends on network settings (e.g. power control level), uplink / downlink data rates and GPRS configuration (e.g. used multislot settings).	
	EGPRS DATA	EGPRS data transfer in progress. Power consumption depends on network settings (e.g. power control level), uplink / downlink data rates and EGPRS configuration (e.g. used multislot settings).	
	UMTS DATA	UMTS data transfer in progress. Power consumption depends on network settings (e.g. TPC Pattern) and data transfer rate.	
	HSPA DATA	HSPA data transfer in progress. Power consumption depends on network settings (e.g. TPC Pattern) and data transfer rate.	
	LTE DATA	LTE data transfer in progress. Power consumption depends on network settings (e.g. TPC Pattern) and data transfer rate.	
Power Down	Normal shutdown after sending the AT^SMSO command. Software is not active. Interfaces are not accessible. Operating voltage (connected to BATT+) remains applied.		
Airplane mode	Airplane mode shuts down the radio part of the module, causes the module to log off from the GSM/GPRS network and disables all AT commands whose execution requires a radio connection.  Airplane mode can be controlled by AT command (see [1]).		

## 3.2 Power Supply

PLS8-E needs to be connected to a power supply at the SMT application interface - 4 lines each BATT+ and GND. There are two separate voltage domains for BATT+:

- BATT+\_RF with 2 lines for the RF power amplifier supply
- BATT+ with 2 lines for the general power management.

The main power supply from an external application has to be a single voltage source and has to be expanded to two sub paths (star structure). Each voltage domain must be decoupled by application with low ESR capacitors ( $\geq$  47 $\mu$ F MLCC @ BATT+;  $\geq$  4x47 $\mu$ F MLCC @ BATT+\_RF) as close as possible to LGA pads. Figure 3 shows a sample circuit for decoupling capacitors for BATT+.

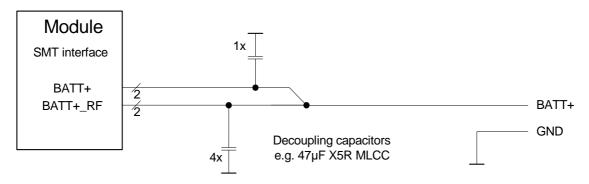


Figure 3: Decoupling capacitor(s) for BATT+

The power supply of PLS8-E must be able to provide the peak current during the uplink transmission.

All key functions for supplying power to the device are handled by the power management IC. It provides the following features:

- Stabilizes the supply voltages for the baseband using switching regulators and low drop linear voltage regulators.
- Switches the module's power voltages for the power-up and -down procedures.
- Delivers, across the VEXT line, a regulated voltage for an external application.
- LDO to provide SIM power supply.

### 3.2.1 Minimizing Power Losses

When designing the power supply for your application please pay specific attention to power losses. Ensure that the input voltage  $V_{BATT+}$  never drops below 3.3V on the PLS8-E board, not even in a transmit burst where current consumption can rise to typical peaks of 2A. It should be noted that PLS8-E switches off when exceeding these limits. Any voltage drops that may occur in a transmit burst should not exceed 400mV to ensure the expected RF performance in 2G networks.

The module switches off if the minimum battery voltage (V<sub>BATT</sub>min) is reached.

### Example:

 $V_1$ min = 3.3V Dmax = 0.4V

V main Vinnin i Dimay

 $V_{BATT}$ min =  $V_{I}$ min + Dmax  $V_{BATT}$ min = 3.3V + 0.4V = 3.7V

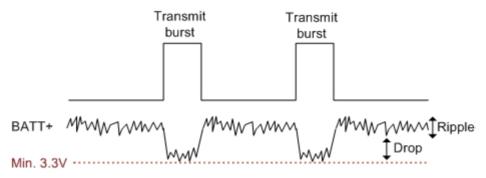


Figure 4: Power supply limits during transmit burst

## 3.2.2 Monitoring Power Supply by AT Command

To monitor the supply voltage you can use the AT^SBV command which returns the averaged value related to BATT+ and GND at the SMT application interface.

The module continuously measures the voltage at intervals depending on the operating mode of the RF interface. The duration of measuring ranges from 0.5s in DATA mode to 50s when PLS8-E is in Limited Service (deregistered). The displayed voltage (in mV) is averaged over the last measuring period before the AT^SBV command was executed.

### 3.3 Power-Up / Power-Down Scenarios

In general, be sure not to turn on PLS8-E while it is beyond the safety limits of voltage and temperature stated in Section 5.1. PLS8-E would immediately switch off after having started and detected these inappropriate conditions. In extreme cases this can cause permanent damage to the module.

#### 3.3.1 Turn on PLS8-E

When the PLS8-E module is in Power-down mode, it can be started to Normal mode by driving the IGT (ignition) line to ground. it is recommended to use an open drain/collector driver to avoid current flowing into this signal line. Pulling this signal low triggers a power-on sequence. To turn on PLS8-E IGT has to be kept active at least 100ms. After turning on PLS8-E IGT should be set inactive to prevent the module from turning on again after a shut down by AT command or EMERG\_OFF. For details on signal states during startup see also Section 3.3.2.

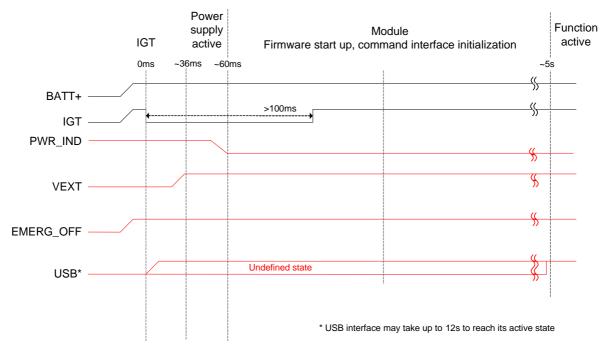


Figure 5: Power-on with IGT

Note: After power up IGT should remain high. Also note that with a USB connection the USB host may take up to 12 seconds to set up the virtual COM port connection.

The module's ready state can be checked by polling. To do so, try to send characters (e.g. "at") until the module is responding.

## 3.3.2 Signal States after Startup

Table 7 describes the various states each interface signal passes through after startup and during operation.

Signals are in an initial state while the module is initializing. Once the startup initialization has completed, i.e. when the software is running, all signals are in defined state. The state of several signals will change again once the respective interface is activated or configured by AT command.

Table 7: Signal states

Signal name	Power on reset	Startup phase	State after first firmware initialization
	Duration appr. 60ms	Duration appr. 4s	After 4-5s
CCIN	PD and PU (24k)	PU(24k)	I, PU(24k)
CCRST	Not driven (similar PD)	Not driven (similar PD)	O, L <sup>1</sup>
			O, H <sup>2</sup>
CCIO	PD(10k)	PD(10k)	PD(10k) <sup>1</sup>
			PU(10k) <sup>2</sup>
CCCLK	Not driven (similar PD)	Not driven (similar PD)	O, L <sup>1</sup>
			Clock <sup>2</sup>
CCVCC	Off	Off	Off <sup>1</sup>
			1.8V/3V <sup>2</sup>
PWR_IND	Z	O, L	O, L
STATUS	PD	PD	PD
EMERG_OFF	PU	I, PU	I, PU
IGT	I, PU	I, PU	I, PU
GPIO110 <sup>3</sup>	PD	PD	PD

L = Low level H = High level I = Input	PD = Pull down resistor with appr. 100k <sup>4</sup> PD(k) = Pull down resistor withk PU = Pull up resistor with appr. 100k PLI(_k) = Pull up resistor withk
O = Output	PU(k) = Pull up resistor withk Z = High impedance

<sup>&</sup>lt;sup>1.</sup> If CCIN = High level

<sup>&</sup>lt;sup>2.</sup> If CCIN = Low level

<sup>&</sup>lt;sup>3.</sup> Please note that during its startup phase the GPIO8 signal will be in an active low state for appr. 80ms.

<sup>&</sup>lt;sup>4.</sup> Internal pulls are implemented using JFETs; strengths vary between devices, possible range: 55k...390k

### 3.3.3 Turn off PLS8-E Using AT Command

The best and safest approach to powering down PLS8-E is to issue the AT^SMSO command. This procedure lets PLS8-E log off from the network and allows the software to enter into a secure state and safe data before disconnecting the power supply. The mode is referred to as Power Down mode. After sending AT^SMSO do not enter any other AT commands. To verify that the module turned off it is possible to monitor the PWR\_IND signal. A high state of the PWR\_IND signal line indicates that the module is being switched off as shown in Figure 6.

Be sure not to disconnect the supply voltage  $V_{BATT+}$  before the module's switch off procedure has been completed and the VEXT signal has gone low. Otherwise you run the risk of losing data. Signal states during switch off are shown in Figure 6.

While PLS8-E is in Power-down mode the application interface is switched off and must not be fed from any other source. Therefore, your application must be designed to avoid any current flow into any digital signal lines of the application interface. No special care is required for the USB interface which is protected from reverse current.

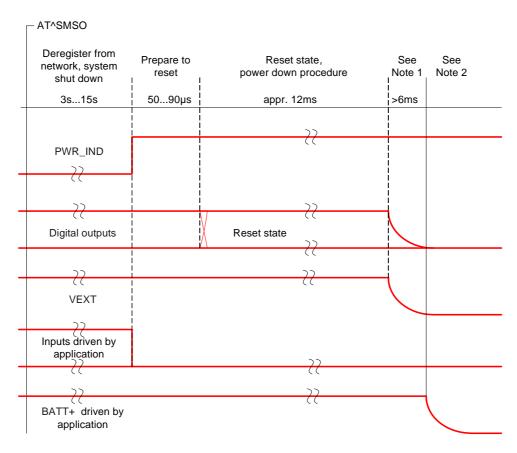


Figure 6: Signal states during turn-off procedure

- Note 1: Depending on capacitance load from host application
- Note 2: The power supply voltage (BATT+) may be disconnected resp. switched off only after the VEXT went low.
- Note 3: After module shutdown by means of AT command is completed, please allow for a time period of at least 1s before restarting the module.

## 3.3.4 Turn off PLS8-E Using IGT Line

The IGT line can be used to switch off PLS8-E. If the module is on, the IGT line must be asserted for at least 2.1s before being released. The module switches off after the line is released. The switch-off routine is identical with the procedure initiated by AT^SMSO, i.e. the software performs an orderly shutdown as described in Section 3.3.3. Before switching off the module wait at least 12 seconds after startup.



Figure 7: Timing of IGT if used to switch off the module

### 3.3.5 Automatic Shutdown

Automatic shutdown takes effect if:

- The PLS8-E board is exceeding the critical limits of overtemperature or undertemperature
- Undervoltage or overvoltage is detected

The automatic shutdown procedure is equivalent to the power down initiated with the AT^SMSO command, i.e. PLS8-E logs off from the network and the software enters a secure state avoiding loss of data.

Alert messages transmitted before the device switches off are implemented as Unsolicited Result Codes (URCs). The presentation of the temperature URCs can be enabled or disabled with the AT commands AT^SCTM. The URC presentation mode varies with the condition, please see Section 3.3.5.1 to Section 3.3.5.3 for details. For further instructions on AT commands refer to [1].

### 3.3.5.1 Thermal Shutdown

The board temperature is constantly monitored by an internal NTC resistor located on the PCB. The values detected by the NTC resistor are measured directly on the board and therefore, are not fully identical with the ambient temperature.

Each time the board temperature goes out of range or back to normal, PLS8-E instantly displays an alert (if enabled).

- URCs indicating the level "1" or "-1" allow the user to take appropriate precautions, such as
  protecting the module from exposure to extreme conditions. The presentation of the URCs
  depends on the settings selected with the AT^SCTM write command:
  - AT^SCTM=1: Presentation of URCs is always enabled.
  - AT^SCTM=0 (default): Presentation of URCs is enabled during the 15 second guard period after start-up of PLS8-E. After expiry of the 15 second guard period, the presentation will be disabled, i.e. no URCs with alert levels "1" or "-1" will be generated.
- URCs indicating the level "2" or "-2" are instantly followed by an orderly shutdown. The presentation of these URCs is always enabled, i.e. they will be output even though the factory setting AT^SCTM=0 was never changed.

The maximum temperature ratings are stated in Section 5.2. Refer to Table 8 for the associated URCs.

Table 8: Temperature dependent behavior

Sending temperature alert (15sec after PLS8-E start-up, otherwise only if URC presentation enabled)		
^SCTM_B: 1	Caution: Board close to overtemperature limit, i.e., board is 5°C below overtemperature limit.	
^SCTM_B: -1	Caution: Board close to undertemperature limit, i.e., board is 5°C above undertemperature limit.	
^SCTM_B: 0	Board back to uncritical temperature range, i.e., board is 6°C below its over- or above its undertemperature limit.	
Automatic shutdown	(URC appears no matter whether or not presentation was enabled)	
^SCTM_B: 2	Alert: Board equal or beyond overtemperature limit. PLS8-E switches off.	
^SCTM_B: -2	Alert: Board equal or below undertemperature limit. PLS8-E switches off.	

The AT^SCTM command can also be used to check the present status of the board. Depending on the selected mode, the read command returns the current board temperature in degrees Celsius or only a value that indicates whether the board is within the safe or critical temperature range. See [1] for further instructions.

### 3.3.5.2 Undervoltage Shutdown

If the measured battery voltage is no more sufficient to set up a call the following URC will be presented:

^SBC: Undervoltage.

The URC indicates that the module is close to the undervoltage threshold. If undervoltage persists the module keeps sending the URC several times before switching off automatically.

This type of URC does not need to be activated by the user. It will be output automatically when fault conditions occur.

### 3.3.5.3 Overvoltage Shutdown

The overvoltage shutdown threshold is 100mV above the maximum supply voltage V<sub>BATT+</sub> specified in Table 17.

When the supply voltage approaches the overvoltage shutdown threshold the module will send the following URC:

**^SBC**: Overvoltage warning

This alert is sent once.

When the overvoltage shutdown threshold is exceeded the module will send the following URC ^SBC: Overvoltage shutdown before it shuts down cleanly:

This type of URC does not need to be activated by the user. It will be output automatically when fault conditions occur.

Keep in mind that several PLS8-E components are directly linked to BATT+ and, therefore, the supply voltage remains applied at major parts of PLS8-E, even if the module is switched off. Especially the power amplifier is very sensitive to high voltage and might even be destroyed.

## 3.3.6 Turn off PLS8-E in Case of Emergency

Caution: Use the EMERG\_OFF line only when, due to serious problems, the software is not responding for more than 5 seconds. Pulling the EMERG\_OFF line causes the loss of all information stored in the volatile memory. Therefore, this procedure is intended only for use in case of emergency, e.g. if PLS8-E does not respond, if reset or shutdown via AT command fails.

The EMERG\_OFF line is available on the application interface and can be used to switch off the module. To control the EMERG\_OFF line it is recommended to use an open drain / collector driver.

To switch off, the EMERG\_OFF line must be pulled to ground for longer than 40ms. After the 40ms and an additional delay period of 500ms the module shuts down as shown in Figure 8.

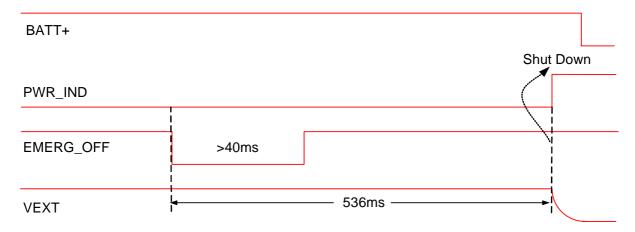


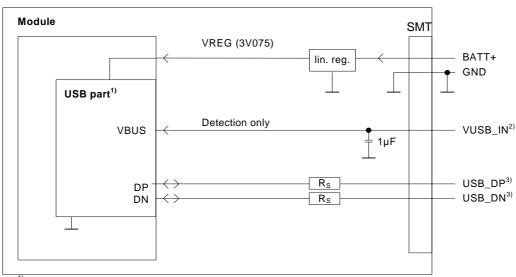
Figure 8: Shutdown by EMERG\_OFF signal

Please note that the power supply voltage (BATT+) may be disconnected resp. switched off only after having reached Shut Down as indicated by the PWR\_IND signal going high. The power supply has to be available (again) before the module is restarted.

### 3.4 USB Interface

PLS8-E supports a USB 2.0 High Speed (480Mbit/s) device interface that is Full Speed (12Mbit/s) compliant. The USB interface is primarily intended for use as command and data interface and for downloading firmware.

The USB host is responsible for supplying the VUSB\_IN line. This line is for voltage detection only. The USB part (driver and transceiver) is supplied by means of BATT+. This is because PLS8-E is designed as a self-powered device compliant with the "Universal Serial Bus Specification Revision 2.0".



<sup>1)</sup> All serial (including R<sub>S</sub>) and pull-up resistors for data lines are implemented.

Figure 9: USB circuit

To properly connect the module's USB interface to the host a USB 2.0 compatible connector is required. For more information on the USB related signals see Table 17. Furthermore, the USB modem driver distributed with PLS8-E needs to be installed.

\_

<sup>&</sup>lt;sup>2)</sup> Since VUSB\_IN is used for detection only it is recommended not to add any further blocking capacitors on the VUSB\_IN line.

<sup>&</sup>lt;sup>3)</sup> If the USB interface is operated in High Speed mode (480MHz), it is recommended to take special care routing the data lines USB\_DP and USB\_DN. Application layout should in this case implement a differential impedance of 900hm for proper signal integrity.

<sup>1.</sup> The specification is ready for download on http://www.usb.org/developers/docs/

### 3.5 UICC/SIM/USIM Interface

PLS8-E has an integrated UICC/SIM/USIM interface compatible with the 3GPP 31.102 and ETSI 102 221. This is wired to the host interface in order to be connected to an external SIM card holder. Five pads on the SMT application interfaceare reserved for the SIM interface.

The UICC/SIM/USIM interface supports 3V and 1.8V SIM cards. Please refer to Table 17 for electrical specifications of the UICC/SIM/USIM interface lines depending on whether a 3V or 1.8V SIM card is used.

The CCIN signal serves to detect whether a tray (with SIM card) is present in the card holder. Using the CCIN signal is mandatory for compliance with the GSM 11.11 recommendation if the mechanical design of the host application allows the user to remove the SIM card during operation. To take advantage of this feature, an appropriate SIM card detect switch is required on the card holder. For example, this is true for the model supplied by Molex, which has been tested to operate with PLS8-E and is part of the Cinterion reference equipment submitted for type approval. See Chapter 9 for Molex ordering numbers.

 Table 9: Signals of the SIM interface (SMT application interface)

Signal	Description
GND	Ground connection for SIM. Optionally a separate SIM ground line using e.g., pad N11 may be used to improve EMC.
CCCLK	Chipcard clock
CCVCC	SIM supply voltage.
CCIO	Serial data line, input and output.
CCRST	Chipcard reset
CCIN	Input on the baseband processor for detecting a SIM card tray in the holder. If the SIM is removed during operation the SIM interface is shut down immediately to prevent destruction of the SIM. The CCIN signal is active low.  The CCIN signal is mandatory for applications that allow the user to remove the SIM card during operation.  The CCIN signal is solely intended for use with a SIM card. It must not be used for any other purposes. Failure to comply with this requirement may invalidate the type approval of PLS8-E.

Note: No guarantee can be given, nor any liability accepted, if loss of data is encountered after removing the SIM card during operation. Also, no guarantee can be given for properly initializing any SIM card that the user inserts after having removed the SIM card during operation. In this case, the application must restart PLS8-E.

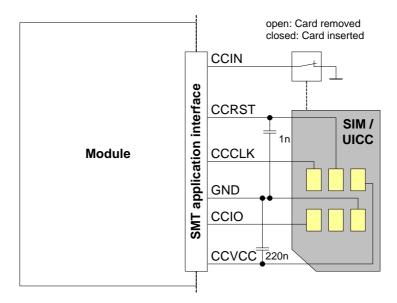


Figure 10: UICC/SIM/USIM interface

The total cable length between the SMT application interface pads on PLS8-E and the pads of the external SIM card holder must not exceed 100mm in order to meet the specifications of 3GPP TS 51.010-1 and to satisfy the requirements of EMC compliance.

To avoid possible cross-talk from the CCCLK signal to the CCIO signal be careful that both lines are not placed closely next to each other. A useful approach is using the GND line to shield the CCIO line from the CCCLK line.

An example for an optimized ESD protection for the SIM interface is shown in Section 3.5.1.

### 3.5.1 Enhanced ESD Protection for SIM Interface

To optimize ESD protection for the SIM interface it is possible to add ESD diodes to the SIM interface lines as shown in the example given in Figure 11.

The example was designed to meet ESD protection according ETSI EN 301 489-1/7: Contact discharge: ± 4kV, air discharge: ± 8kV.

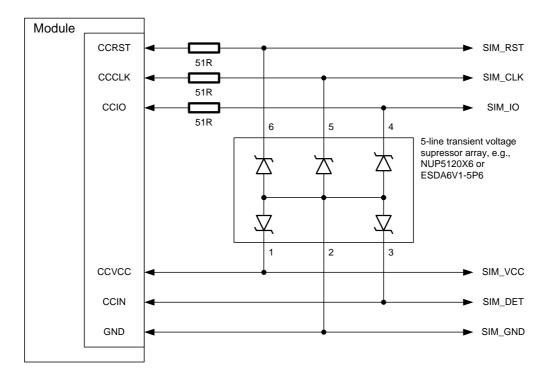


Figure 11: SIM interface - enhanced ESD protection

3.6 Analog-to-Digital Converter (ADC)

## 3.6 Analog-to-Digital Converter (ADC)

ADC1\_IN and ADC2\_IN are prepared for general purpose and are designed to measure two independent voltages in the range of 0.3V to 3.075V.

### 3.7 **GPIO** Interface

PLS8-E has 10 GPIOs for external hardware devices. Each GPIO can be configured for use as input or output. All settings are AT command controlled.

The IO port driver has to be open before using and configuring GPIOs. Before changing the configuration of a GPIO pin (e.g. input to output) the pin has to be closed. If the GPIO pins are not configured or the pins/driver were closed, the GPIO pins are high-Z with pull down resistor. If a GPIO is configured to input, the pin has high-Z without pull resistor. Internal pulls are implemented using JFETs; strengths vary between devices, possible range: 55k...390k.

## 3.8 Control Signal

## 3.8.1 PWR\_IND Signal

PWR\_IND notifies the on/off state of the module. High state of PWR\_IND indicates that the module is switched off. The state of PWR\_IND immediately changes to low when IGT is pulled low. For state detection an external pull-up resistor is required.

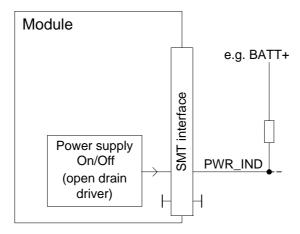


Figure 12: PWR\_IND signal

#### 4 Antenna Interfaces

#### 4.1 GSM/UMTS/LTE Antenna Interface

The PLS8-E GSM/UMTS/LTE antenna interface comprises a GSM/UMTS/LTE main antenna as well as a UMTS/LTE Rx diversity/MIMO antenna to improve signal reliability and quality<sup>1</sup>. The interface has an impedance of  $50\Omega$ . PLS8-E is capable of sustaining a total mismatch at the antenna interface without any damage, even when transmitting at maximum RF power.

The external antennas must be matched properly to achieve best performance regarding radiated power, modulation accuracy and harmonic suppression. Matching networks are not included on the PLS8-E PCB and should be placed in the host application, if the antenna does not have an impedance of  $50\Omega$ .

Regarding the return loss PLS8-E provides the following values in the active band:

Table 10: Return loss in the active band

State of module	Return loss of module	Recommended return loss of application
Receive	≥ 8dB	≥ 12dB
Transmit	not applicable	≥ 12dB
Idle	≤ 5dB	not applicable

PLS8-E\_HD\_v01.000a Confidential / Preliminary

<sup>&</sup>lt;sup>1.</sup> By delivery default the UMTS/LTE Rx diversity/MIMO antenna is configured as available for the module since its usage is mandatory for LTE. Please refer to [1] for details on how to configure antenna settings.

#### 4.1.1 Antenna Installation

The antenna is connected by soldering the antenna pads (ANT\_MAIN; ANT\_DRX\_MIMO) and their neighboring ground pads directly to the application's PCB.

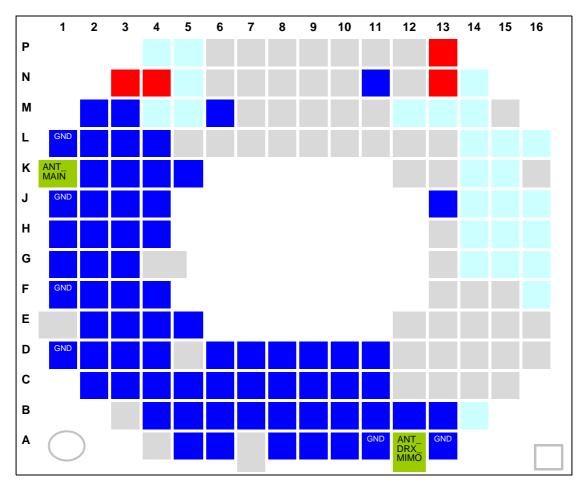


Figure 13: Antenna pads (bottom view)

The distance between the antenna pads and their neighboring GND pads has been optimized for best possible impedance. To prevent mismatch, special attention should be paid to these pads on the application' PCB.

The wiring of the antenna connection, starting from the antenna pad to the application's antenna should result in a  $50\Omega$  line impedance. Line width and distance to the GND plane need to be optimized with regard to the PCB's layer stack. Some examples are given in Section 4.1.2.

To prevent receiver desensitization due to interferences generated by fast transients like high speed clocks on the external application PCB, it is recommended to realize the antenna connection line using embedded Stripline rather than Micro-Stripline technology. Please see Section 4.1.2 for examples of how to design the antenna connection in order to achieve the required  $50\Omega$  line impedance.

For type approval purposes, the use of a  $50\Omega$  coaxial antenna connector (U.FL-R-SMT) might be necessary. In this case the U.FL-R-SMT connector should be placed as close as possible to PLS8-E's antenna pad.

### 4.1.2 RF Line Routing Design

### 4.1.2.1 Line Arrangement Examples

Several dedicated tools are available to calculate line arrangements for specific applications and PCB materials - for example from http://www.polarinstruments.com/ (commercial software) or from http://web.awrcorp.com/Usa/Products/Optional-Products/TX-Line/ (free software).

#### **Embedded Stripline**

This below figure shows line arrangement examples for embedded stripline.



Figure 14: Embedded Stripline line arrangement

#### **Micro-Stripline**

This section gives two line arrangement examples for micro-stripline.

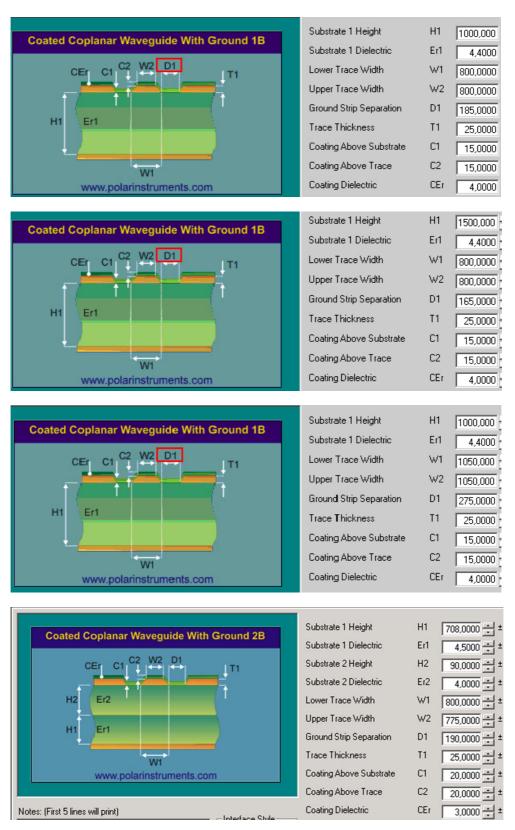


Figure 15: Micro-Stripline line arrangement samples

### 4.1.2.2 Routing Example

#### Interface to RF Connector

Figure 16 shows a sample connection of a module's antenna pad at the bottom layer of the module PCB with an application PCB's coaxial antenna connector. Line impedance depends on line width, but also on other PCB characteristics like dielectric, height and layer gap. The sample stripline width of 0.33mm is recommended for an application with a PCB layer stack resembling the one of the PLS8-E evaluation board shown in Figure 17. For different layer stacks the stripline width will have to be adapted accordingly.

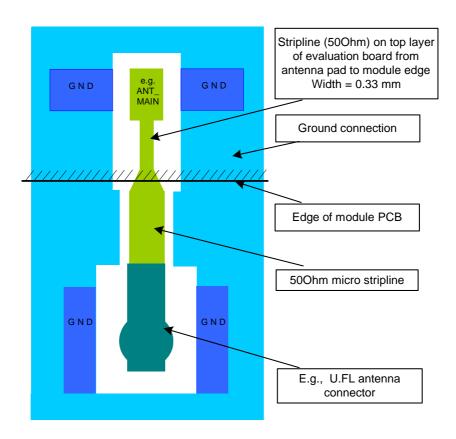


Figure 16: Routing to application's RF connector

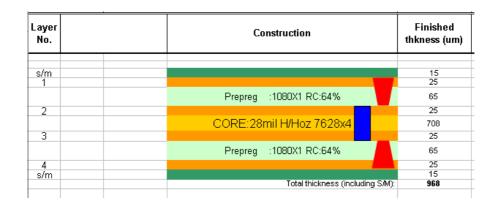


Figure 17: PLS8-E evaluation board layer table

## 5 Electrical, Reliability and Radio Characteristics

## 5.1 Absolute Maximum Ratings

The absolute maximum ratings stated in Table 11 are stress ratings under any conditions. Stresses beyond any of these limits will cause permanent damage to PLS8-E.

Table 11: Absolute maximum ratings

Parameter	Min	Max	Unit
Supply voltage BATT+	-0.5	+6.0	V
Voltage at all digital lines in POWER DOWN mode	-0.5	+0.5	V
Voltage at digital lines in normal operation	-0.5	+2.3	V
Voltage at SIM/USIM interface, CCVCC 1.8V in normal operation	-0.5	+2.3	V
Voltage at SIM/USIM interface, CCVCC 3.0V in normal operation	-0.5	+3.4	V
Voltage at ADC pins if the module is powered by BATT+	-0.5	+3.5	V
Voltage at ADC pins if the module is not powered	-0.5	+0.5	V
VEXT maximum current shorted to GND		-300	mA
VUSB_IN, USB_DN, USB_DP	-0.3	5.75	V
Voltage at PWR_IND line	-0.5	5.5	V
PWR_IND input current if PWR_IND= low		2	mA
Voltage at following signals: IGT, EMERG_OFF	-0.5	2.5	V

#### 5.2 Operating Temperatures

Table 12: Board temperature

Parameter	Min	Тур	Max	Unit
Operating temperature range <sup>1</sup> Normal temperature range Extreme temperature range	+15 -30	+25	+55 +85	°C
Extended temperature range <sup>2</sup>	-40		+95	°C
Automatic shutdown <sup>3</sup> Temperature measured on PLS8-E board	<-40		>+95	°C

<sup>&</sup>lt;sup>1.</sup> Operating temperature range according to 3GPP type approval specification.

See also Section 3.3.5 for information about the NTC for on-board temperature measurement, automatic thermal shutdown and alert messages.

Note that within the specified operating temperature ranges the board temperature may vary to a great extent depending on operating mode, used frequency band, radio output power and current supply voltage.

### **5.2.1** Temperature Allocation Model

The temperature allocation model shown in Table 13 assumes shares of a module's average lifetime of 10 years (given in %) during which the module is operated at certain temperatures.

Table 13: Temperature allocation model

Module lifetime share (in %) <sup>1</sup>	6	20	65	7	1	1
Module Temperature (in °C)	-40	20	40	75	85	95

<sup>&</sup>lt;sup>1</sup> Based on an assumed average module lifetime of 10 years (=100%).

Any deviations from the above temperature allocation model may reduce the module's life span, for example if the module is operated close to the maximum automatic shutdown temperature not only for 1% but for 20% of its product life.

Extended operation allows normal mode data transmissions for limited time until automatic thermal shutdown takes effect.

Within the extended temperature range (outside the operating temperature range) there will be no inefficient use of the radio spectrum and no harm to the radio network. Also, there should not be any unrecoverable malfunctioning. General performance parameters like Pout or RX sensitivity however may be reduced in their values. The module's life time may also be affected, if deviating from a general temperature allocation model (for details see Section 5.2.1).

<sup>3.</sup> Due to temperature measurement uncertainty, a tolerance on the stated shutdown thresholds may occur. The possible deviation is in the range of ± 2°C at the overtemperature and undertemperature limit.

### 5.3 Storage Conditions

The conditions stated below are only valid for modules in their original packed state in weather protected, non-temperature-controlled storage locations. Normal storage time under these conditions is 12 months maximum. The modules will be delivered in a packaging that meets the requirements according "IPD/JEDEC J-STD-033B.1" for Low Temperature Carriers.

Table 14: Storage conditions

Туре		Condition	Unit	Reference
Humidity relativ	e: Low High	10 90 at 40°C	%	CbIPC/JEDEC J-STD-033A
Air pressure:	Low High	70 106	kPa	IEC TR 60271-3-1: 1K4 IEC TR 60271-3-1: 1K4
Movement of su	urrounding air	1.0	m/s	IEC TR 60271-3-1: 1K4
Water: rain, drip frosting	pping, icing and	Not allowed		
Radiation:	Solar Heat	1120 600	W/m <sup>2</sup>	ETS 300 019-2-1: T1.2, IEC 60068-2-2 Bb ETS 300 019-2-1: T1.2, IEC 60068-2-2 Bb
Chemically acti	ve substances	Not recom- mended		IEC TR 60271-3-1: 1C1L
Mechanically ad stances	ctive sub-	Not recom- mended		IEC TR 60271-3-1: 1S1
Vibration sinusoidal: Displacement Acceleration Frequency range		1.5 5 2-9 9-200	mm m/s <sup>2</sup> Hz	IEC TR 60271-3-1: 1M2
Shocks: Shock spec Duration Acceleratio		semi-sinusoidal 1 50	ms m/s <sup>2</sup>	IEC 60068-2-27 Ea

### 5.4 Reliability Characteristics

The test conditions stated below are an extract of the complete test specifications.

Table 15: Summary of reliability test conditions

Type of test	Conditions	Standard
Vibration	Frequency range: 10-20Hz; acceleration: 5g Frequency range: 20-500Hz; acceleration: 20g Duration: 20hper axis; 3 axes	DIN IEC 60068-2-6 <sup>1</sup>
Shock half-sinus	Acceleration: 500g Shock duration: 1msec 1 shock per axis 6 positions (± x, y and z)	DIN IEC 60068-2-27
Dry heat	Temperature: +70 ±2×C Test duration: 16h Humidity in the test chamber: < 50%	EN 60068-2-2 Bb ETS 300 019-2-7
Temperature change (shock)	Low temperature: -40×C ±2×C High temperature: +85×C ±2×C Changeover time: < 30s (dual chamber system) Test duration: 1h Number of repetitions: 100	DIN IEC 60068-2-14 Na ETS 300 019-2-7
Damp heat cyclic	High temperature: +55×C ±2×C Low temperature: +25×C ±2×C Humidity: 93% ±3% Number of repetitions: 6 Test duration: 12h + 12h	DIN IEC 60068-2-30 Db ETS 300 019-2-5
Cold (constant exposure)	Temperature: -40 ±2×C Test duration: 16h	DIN IEC 60068-2-1

<sup>1.</sup> For reliability tests in the frequency range 20-500Hz the Standard's acceleration reference value was increased to 20g.

## 5.4.1 Bending Tests

From experience with other modules an elongation of up to 200µm/m is acceptable for PLS8-E modules as a result of bending strains.

Tests (based on EN 60068-2-21) showed that if applying a force of 10N at the middle of the module, i.e., the evaluation module with the actual PLS8-E module soldered onto the evaluation PCB as shown in Figure 18, the possible elongation is clearly below the value of  $200\mu m/m$ . Therefore, a force of 10N is recommended as maximum force.

Please note that these values only apply for a one-off short stress. The module will have to be mounted free of any strains and without being exposed to dynamic pressures.

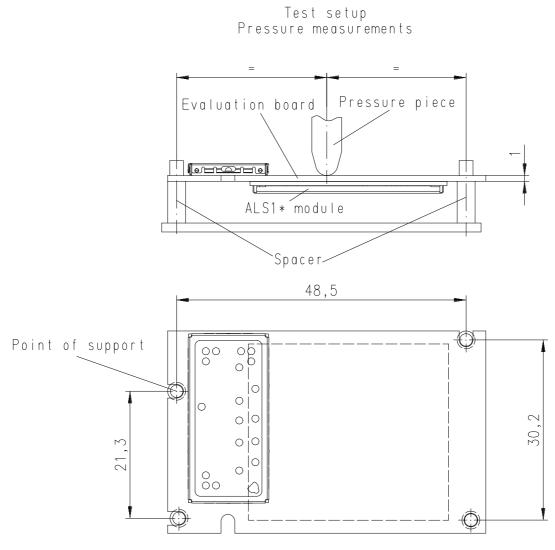


Figure 18: Bending test setup

## 5.5 Pad Assignment and Signal Description

The SMT application interface on the PLS8-E provides connecting pads to integrate the module into external applications. The following Table 16 lists the pads' assignments, Figure 19 (bottom view) and Figure 20 (top view) show the connecting pads' numbering plan.

Please note that pads marked "rfu" (reserved for future use) and further qualified as "dnu" (do not use) may be soldered but should not be connected to an external application.

Because with surface mount modules the heat is transported through the solder pads to the external application's PCB, it is generally recommended to solder all pads.

Table 16: Overview: Pad assignments<sup>1</sup>

	O. Overview. Fac assigning				
Pad	Signal Name	Pad	Signal Name	Pad	Signal Name
No.		No.		No.	
A4	nc	E2	GND	L2	GND
A5	GND	E3	GND	L3	GND
A6	GND	E4	GND	L4	GND
A7	rfu (dnu)	E5	GND	L5	rfu (dnu)
A8	GND	E12	rfu (dnu)	L6	rfu (dnu)
A9	GND	E13	rfu (dnu)	L7	rfu (dnu)
A10	GND	E14	rfu (dnu)	L8	rfu (dnu)
A11	GND	E15	rfu (dnu)	L9	rfu (dnu)
A12	ANT_DRX_MIMO	E16	rfu (dnu)	L10	rfu (dnu)
A13	GND	F1	GND	L11	rfu (dnu)
B3	nc	F2	GND	L12	rfu (dnu)
B4	GND	F3	GND	L13	rfu (dnu)
B5	GND	F4	GND	L14	CCRST
B6	GND	F13	rfu (dnu)	L15	CCCLK
B7	GND		rfu (dnu)		IGT
	GND	F14 F15	rfu (dnu)	L16 M2	GND
B8			CDIO40		GND
B9	GND	F16	GPÌO10	M3	
B10	GND	G1	GND	M4	PWR_IND
B11	GND	G2	GND	M5	VEXT
B12	GND	G3	GND	M6	GND
B13	GND	G4	rfu (dnu)	M7	rfu (dnu)
B14	STATUS	G13	rfu (dnu)	M8	rfu (dnu)
C2	GND	G14	GPÍO7	M9	rfu (dnu)
C3	GND	G15	GPIO8	M10	rfu (dnu)
C4	GND	G16	GPIO9	M11	rfu (dnu)
C5	GND	H1	GND	M12	ADC2_IN
C6	GND	H2	GND	M13	ADC1_IN
C7	GND	H3	GND	M14	CCIN
C8	GND	H4	GND	M15	rfu (dnu)
C9	GND	H13	rfu (dnu)	N3	BATT+_RF
C10	GND	H14	GPÌO4	N4	BATT+ RF
C11	GND	H15	GPIO5	N5	VUSB IN
C12	rfu (dnu)	H16	GPIO6	N6	rfu (dnu)
C13	rfu (dnu)	J1	GND	N7	rfu (dnu)
C14	rfu (dnu)	J2	GND	N8	rfu (dnu)
C15	rfu (dnu)	J3	GND	N9	rfu (dnu)
D1	GND	J4	GND	N10	rfu (dnu)
D2	GND	J13	GND	N11	GND
D3	GND	J14	GPIO1	N12	rfu (dnu)
D4	GND	J15	GPIO2	N13	BATT+
D5	rfu (dnu)	J16	GPI03	N14	EMERG OFF
D6	GND	K1	ANT_MAIN	P4	USB_DP
D6	GND	K2	GND		
				P5	USB_DN
D8	GND	K3	GND	P6	rfu (dnu)
D9	GND	K4	GND	P7	rfu (dnu)
D10	GND	K5	GND	P8	rfu (dnu)
D11	GND	K12	rfu (dnu)	P9	rfu (dnu)
D12	rfu (dnu)	K13	rfu (dnu)	P10	rfu (dnu)
D13	rfu (dnu)	K14	CCIO	P11	rfu (dnu)
D14	rfu (dnu)	K15	CCVCC	P12	rfu (dnu)
D15	rfu (dnu)	K16	rfu (dnu)	P13	BATT+
D16	rfu (dnu)	L1	GND		
E1	rfu (dnu)				
-		•		•	

 $<sup>^{1.}</sup>$  nc = not connected; rfu = reserved for future use; dnu = do not use

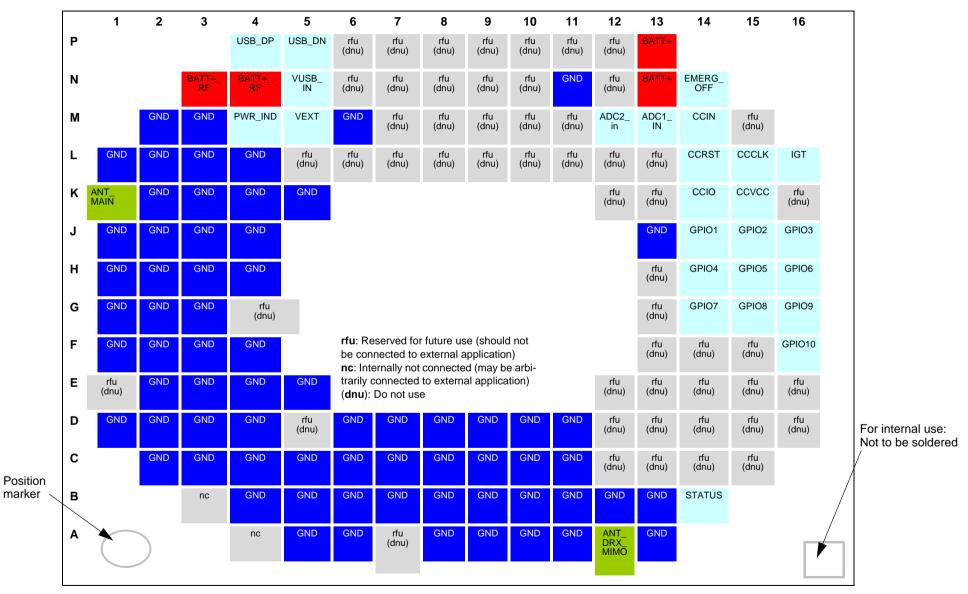


Figure 19: PLS8-E bottom view: Pad assignments

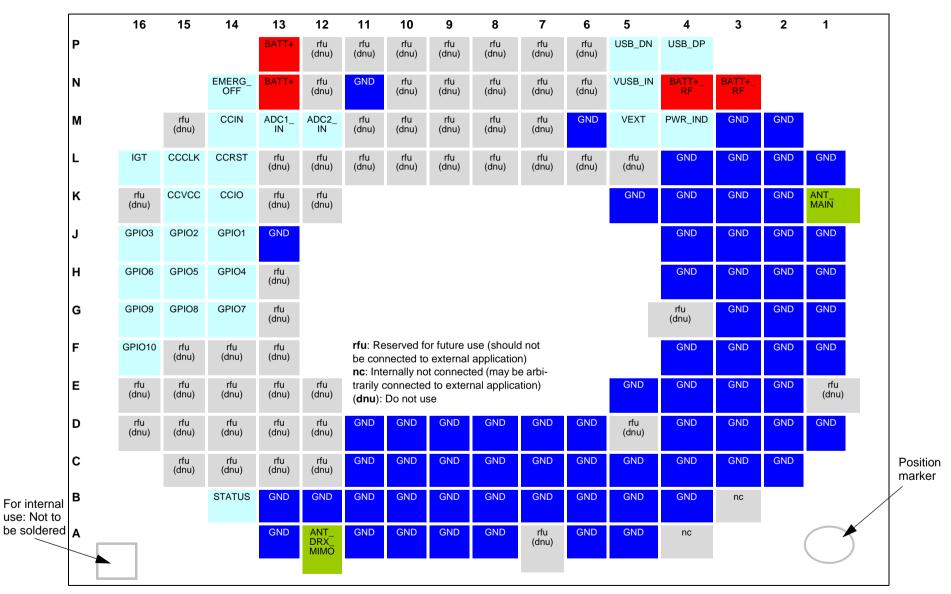


Figure 20: PLS8-E top view: Pad assignments

Please note that the reference voltages listed in Table 17 are the values measured directly on the PLS8-E module. They do not apply to the accessories connected.

Table 17: Signal description

Function	Signal name	Ю	Signal form and level	Comment
Power supply	BATT+_RF	I	$V_l$ max = 4.2V $V_l$ norm = 3.8V $V_l$ min = 3.3V during Tx burst on board Imax $\approx$ 2A, during Tx burst (GSM) $n$ Tx = n x 577 $\mu$ s peak current every 4.615ms	Lines of BATT+ and GND must be connected in parallel for supply purposes because higher peak currents may occur.  Minimum voltage must not fall below 3.3V including
	BATT+	I	$V_l$ max = 4.2V $V_l$ norm = 3.8V $V_l$ min = 3.3V during Tx burst on board Imax = 350mA	drop, ripple, spikes.
Power supply	GND		Ground	Application Ground
External supply voltage	VEXT	0	CLmax = $1\mu$ F $V_O = 1.80V + 1\% - 5\%$ $I_O$ max = $-50$ mA	VEXT may be used for application circuits.  If unused keep line open.  The external digital logic must not cause any spikes or glitches on voltage VEXT.  Do not exeed IOmax
Ignition	IGT	I	$R_{PU} \approx 200 k\Omega$ $V_{OH} max = 1.8V$ $V_{IH} max = 2.1V$ $V_{IH} min = 1.17V$ $V_{IL} max = 300 mV$ $Low impulse width > 100 ms$	This signal switches the module ON.  It is recommended to drive this line low by an open drain or open collector driver connected to GND.
Emer- gency off	EMERG_OFF	I	$\begin{array}{l} {\sf R}_{\sf PU} \approx 40 {\sf k}\Omega \\ {\sf V}_{\sf OH} {\sf max} {=} 1.8 {\sf V} \\ {\sf V}_{\sf IH} {\sf max} = 2.1 {\sf V} \\ {\sf V}_{\sf IH} {\sf min} = 1.17 {\sf V} \\ {\sf V}_{\sf IL} {\sf max} = 300 {\sf mV} \\ {\sim \sim}  \_\_  {\sim \sim} \   {\sf ow impulse width} > 40 {\sf ms} \end{array}$	It is recommended to drive this line low by an open drain or open collector driver connected to GND.  If unused keep line open.
Connectiv- ity status	STATUS	0	V <sub>OL</sub> max = 0.45V at I = 2mA V <sub>OH</sub> min = 1.35V at I = -2mA V <sub>OH</sub> max = 1.85V	Status signalling e.g. with ext. LED circuit
SIM card detection	CCIN	I	$\begin{split} R_{PU} &\approx 24.2 k\Omega \\ V_{OH} max = 1.9 V \\ V_{IH} min &= 1.15 V \\ V_{IH} max = 1.9 V \\ V_{IL} max &= 0.4 V \end{split}$	CCIN = Low, SIM card inserted.  If unused connect to GND.

Table 17: Signal description

Function	Signal name	Ю	Signal form and level	Comment
3V SIM card interface	CCRST	0	$V_{OL}$ max = 0.45V at I = 2mA $V_{OH}$ min = 2.40V at I = -2mA $V_{OH}$ max = 2.9V	Maximum cable length or copper track should be not longer than 100mm to SIM card holder.
	CCIO	I/O	$\begin{split} R_{PU} &\approx 4.89.5 k \Omega \\ V_{IL} max &= 0.76 V \\ V_{IL} min &= -0.3 V \\ V_{IH} min &= 1.98 V \\ V_{IH} max &= 3.35 V \\ \end{split}$ $V_{OL} max &= 0.45 V \text{ at I} = 2 mA \\ V_{OH} min &= 2.57 V \text{ at I} = -0.05 mA \\ V_{OH} max &= 3.08 V \end{split}$	card noider.
	CCCLK	0	$V_{OL}$ max = 0.45V at I = 2mA $V_{OH}$ min = 2.57V at I = -2mA $V_{OH}$ max = 3.08V	
	ccvcc	0	$\begin{aligned} &V_{O}\text{min} = 3.0V \\ &V_{O}\text{typ} = 3.05V \\ &V_{O}\text{max} = 3.08V \\ &I_{O}\text{max} = -50\text{mA} \end{aligned}$	
1.8V SIM card interface	CCRST	0	$V_{OL}$ max = 0.45V at I = 2mA $V_{OH}$ min = 1.35V at I = -2mA $V_{OH}$ max = 1.85V	Maximum cable length or copper track should be not longer than 100mm to SIM
	CCIO	I/O	$\begin{split} R_{I} &\approx 4.89.5 k\Omega \\ V_{IL} max &= 0.62 V \\ V_{IL} min &= -0.3 V \\ V_{IH} min &= 1.20 V \\ V_{IH} max &= 2.1 V \\ \end{split} \\ V_{OL} max &= 0.45 V \ at \ I = 2 mA \\ V_{OH} min &= 1.32 V \ at \ I = -0.05 mA \\ V_{OH} max &= 1.82 V \end{split}$	card holder.
	CCCLK	0	$V_{OL}$ max = 0.45V at I = 2mA $V_{OH}$ min = 1.32V at I = -2mA $V_{OH}$ max = 1.82V	
	CCVCC	0	$V_{O}$ min = 1.75V $V_{O}$ typ = 1.80V $V_{O}$ max = 1.82V $I_{O}$ max = -50mA	

Table 17: Signal description

Function	Signal name	Ю	Signal form and level	Comment
Power indi- cator	PWR_IND	0	$V_{IH}$ max = 5.5V $V_{OL}$ max = 0.4V at Imax = 1mA	PWR_IND (Power Indicator) notifies the module's on/off state.
				PWR_IND is an open collector that needs to be connected to an external pull-up resistor. Low state of the open collector indicates that the module is on. Vice versa, high level notifies the power-down mode.
				Therefore, signal may be used to enable external voltage regulators that supply an external logic for communication with the module, e.g. level converters.
USB	VUSB_IN	I	$\begin{aligned} &V_{IN}\text{min} = 3.0V \\ &V_{IN}\text{max} = 5.75V \\ &I_{I}\text{typ} = 150\mu\text{A} \\ &I_{I}\text{max} = 200\mu\text{A} \\ &\text{Cin=1}\mu\text{F} \end{aligned}$	If the USB interface is not used please connect this line to GND. Since VUSB_IN is used for detection only it is recommended not to add any further blocking capacitors on the VUSB_IN line.
	USB_DN	I/O	All electrical characteristics according	If lines are unused keep
	USB_DP	I/O	to USB Implementers' Forum, USB 2.0 Full or High Speed Specification.	lines open.
				USB High Speed mode operation requires a differential impedance of 90Ω.
GPIO interface	GPIO1 GPIO2 GPIO3 GPIO4 GPIO5 GPIO6 GPIO7 GPIO8 GPIO9 GPIO10	I/O	$V_{IL}$ max = 0.6V at 30 $\mu$ A $V_{IH}$ min = 1.20V at -30 $\mu$ A $V_{IH}$ max = 2V $V_{OL}$ max = 0.45V at I = 2mA $V_{OH}$ min = 1.35V at I = -2mA $V_{OH}$ max = 1.85V	If lines are unused keep lines open.
ADC interface	ADC1_IN, ADC2_IN	I	Full specification compliance range $V_{lmin}>=0.3V$ $V_{lmax}<=3.075V$ Degraded accuracy range $V_{lmin}$ 0.05V 0.3V	If unused keep pin open.  Prepared for general purpose.
			Ridc>1MOhm Resolution: 12 Bit Offset error: <+-10mV Gain error: <1% analog bandwidth: <16kHz conversation time: 853µs	

## 5.6 Power Supply Ratings

Table 18 and Table 19 assemble various voltage supply and current consumption ratings of the module.

Table 18: Voltage supply ratings

	Description	Conditions	Min	Тур	Max	Unit
BATT+	Supply voltage	Directly measured at Module. Voltage must stay within the min/max values, including voltage drop, ripple, spikes	3.3	3.8	4.2	V
	Maximum allowed voltage drop during transmit burst	Normal condition, power control level for Pout max			400	mV
	Voltage ripple	Normal condition, power control level for Pout max @ f <= 250 kHz @ f > 250 kHz			20 16	${\sf mV}_{\sf pp} \ {\sf mV}_{\sf pp}$

Table 19: Current consumption ratings

	Description	Conditions	Typical rating	Unit									
I <sub>BATT+</sub> <sup>1</sup>	OFF State supply current	POWER DOWN	40	μΑ									
	Average GSM /	IDLE (USB disconnected) @ DRX=2	75	mA									
	GPRS supply current	IDLE (USB active) @ DRX=2	90	mA									
		GPRS Data transfer GSM900; PCL=5; 1Tx/4Rx	320	mA									
		GPRS Data transfer GSM900; PCL=5; 2Tx/3Rx	540	mA									
		GPRS Data transfer GSM900; PCL=5; 4Tx/1Rx	930	mA									
		EDGE Data transfer GSM900; PCL=5; 1Tx/4Rx	220	mA									
					EDGE Data transfer GSM900; PCL=5; 2Tx/3Rx	340	mA						
												EDGE Data transfer GSM900; PCL=5; 4Tx/1Rx	570
				GPRS Data transfer GSM1800; PCL=0; 1Tx/4Rx	230	mA							
				GPRS Data transfer GSM1800; PCL=0; 2Tx/3Rx	360	mA							
				GPRS Data transfer GSM1800; PCL=0; 4Tx/1Rx	590	mA							
		EDGE Data transfer GSM1800; PCL=0; 1Tx/4Rx	190	mA									
		EDGE Data transfer GSM1800; PCL=0; 2Tx/3Rx	290	mA									
		EDGE Data transfer GSM1800; PCL=0; 4Tx/1Rx	460	mA									

Table 19: Current consumption ratings

	Description	Conditions	Typical rating	Unit
I <sub>BATT+</sub> 1	Average WCDMA	IDLE (USB disconnected) @ DRX=6	50	mA
	supply current	IDLE (USB active) @ DRX=6	65	mA
		UMTS Data transfer Band I @+24dBm	560	mA
		UMTS Data transfer Band III @+24dBm	620	mA
		UMTS Data transfer Band VIII @+24dBm	500	mA
		HSDPA Data transfer Band I @+24dBm	590	mA
		HSDPA Data transfer Band III @+24dBm	620	mA
		HSDPA Data transfer Band VIII @+24dBm	510	mA
	Average LTE sup-	IDLE (USB disconnected)	55	mA
	ply current <sup>2</sup>	IDLE (USB active)	70	mA
		LTE Data transfer Band 3 @+23dBm	650	mA
		LTE Data transfer Band 7 @+23dBm	640	mA
		LTE Data transfer Band 8 @+23dBm	520	mA
		LTE Data transfer Band 20 @+23dBm	520	mA
I <sub>VUSB_IN</sub>	USB typical and maximum ratings are mentioned in Table 17: VUSB_IN.			

 $<sup>^{\</sup>rm 1.}$  With an impedance of Z<sub>LOAD</sub>=50Ohm at the antenna pads. Measured at 25°C and 4.2V - except for POWER DOWN ratings that were measured at 3.4V.

<sup>&</sup>lt;sup>2</sup> Communication tester settings:

<sup>-</sup> Channel Bandwidth: 5MHz

<sup>-</sup> Number of Resource Blocks: 25 (DL), 1 (UL)

<sup>-</sup> Modulation: QPSK

## 5.7 RF Antenna Interface Characteristics

**Table 20:** RF Antenna interface GSM / UMTS/LTE (at operating temperature range<sup>1</sup>)

Parameter	Conditions	Min.	Typical	Max.	Unit
LTE connectivity <sup>2</sup>	Band 3, 7, 8, 20			•	
Receiver Input Sensitivity @ ARP (ch. bandwidth 5MHz)	LTE 800 Band 20	-97	-103		dBm
	LTE 900 Band 8	-97	-104		dBm
	LTE 1800 Band 3	-97	-103		dBm
	LTE 2600 Band 7	-98	-102		dBm
RF Power @ ARP with 500hm Load	LTE 800 Band 20	+21	+23	+25	dBm
	LTE 900 Band 8	+21	+23	+25	dBm
	LTE 1800 Band 3	+21	+23	+25	dBm
	LTE 2600 Band 7	+21	+23	+25	dBm
UMTS/HSPA connectivity <sup>2</sup>	Band I, III, VIII	1	<b>.</b>	<u> </u>	<b>-</b>
Receiver Input Sensitivity @ ARP	UMTS 900 Band VIII	-103.7	-112		dBm
	UMTS 1800 Band III	-104.7	-111		dBm
	UMTS 2100 Band I	-106.7	-111		dBm
RF Power @ ARP with 500hm Load	UMTS 900 Band VIII	+20.3	+24	+25.3	dBm
	UMTS 1800 Band III	+20.3	+24	+25.3	dBm
	UMTS 2100 Band I	+20.3	+24	+25.3	dBm
GPRS coding schemes	Class 12, CS1 to CS4				
EGPRS	Class 12, MCS1 to MCS9				
GSM Class	Small MS				
Static Receiver input Sensi-	E-GSM 900	-102	-111		dBm
tivity @ ARP	GSM 1800	-102	-110		dBm
RF Power @ ARP	E-GSM 900		33		dBm
with 500hm Load GSM	GSM 1800		30		dBm

Table 20: RF Antenna interface GSM / UMTS/LTE (at operating temperature range<sup>1</sup>)

Parameter		Conditions	Min.	Typical	Max.	Unit
RF Power @	GPRS, 1 TX	E-GSM 900		33		dBm
ARP with 500hm		GSM 1800		30		dBm
Load	EDGE, 1 TX	E-GSM 900		27		dBm
		GSM 1800		26		dBm
	GPRS, 2 TX	E-GSM 900		33		dBm
		GSM 1800		30		dBm
	EDGE, 2 TX	E-GSM 900		27		dBm
		GSM 1800		26		dBm
	GPRS, 3 TX	E-GSM 900		33		dBm
		GSM 1800		30		dBm
	EDGE, 3 TX	E-GSM 900		27		dBm
		GSM 1800		26		dBm
	GPRS, 4 TX	E-GSM 900		33		dBm
		GSM 1800		30		dBm
	EDGE, 4 TX	E-GSM 900		27		dBm
		GSM 1800		26		dBm

<sup>1.</sup> At restricted temperature range no active power reduction is implemented - any deviations are hardware related.

 $<sup>^{\</sup>rm 2.}$  Applies also to UMTS/LTE Rx diversity/MIMO antenna.

#### 5.8 Electrostatic Discharge

The module is not protected against Electrostatic Discharge (ESD) in general. Consequently, it is subject to ESD handling precautions that typically apply to ESD sensitive components. Proper ESD handling and packaging procedures must be applied throughout the processing, handling and operation of any application that incorporates a PLS8-E module.

Special ESD protection provided on PLS8-E:

BATT+: Inductor/capacitor

An example for an enhanced ESD protection for the SIM interface is shown in Section 3.5.1.

The remaining interfaces of PLS8-E with the exception of the antenna interface are not accessible to the user of the final product (since they are installed within the device) and are therefore only protected according to the ANSI/ESDA/JEDEC JS-001-2011 requirements.

PLS8-E has been tested according to the following standards. Electrostatic values can be gathered from the following table.

Table 21: Electrostatic values

Specification / Requirements	Contact discharge	Air discharge		
ANSI/ESDA/JEDEC JS-001-2011				
All SMT interfaces	± 1kV Human Body Model	n.a.		
JESD22-A114-F				
All SMT interfaces	± 500V Charge Device Model (CDM)	n.a.		
ETSI EN 301 489-1/7				
BATT+	± 4kV	± 8kV		

Note: Please note that the values may vary with the individual application design. For example, it matters whether or not the application platform is grounded over external devices like a computer or other equipment, such as the Cinterion Wireless Modules reference application described in Chapter 8.

## 6 Mechanics, Mounting and Packaging

#### 6.1 Mechanical Dimensions of PLS8-E

Figure 21 shows a 3D view<sup>1</sup> of PLS8-E and provides an overview of the board's mechanical dimensions. For further details see Figure 22.

Length: 33mm Width: 29mm Height: 2.2mm

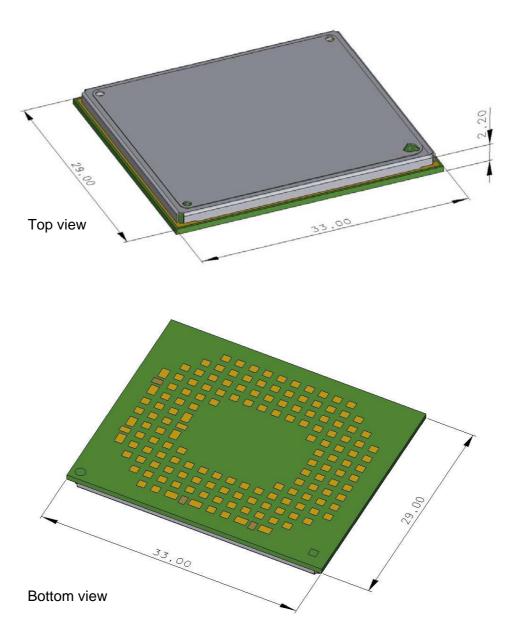


Figure 21: PLS8-E - top and bottom view

<sup>&</sup>lt;sup>1.</sup> The coloring of the 3D view does not reflect the module's real color.

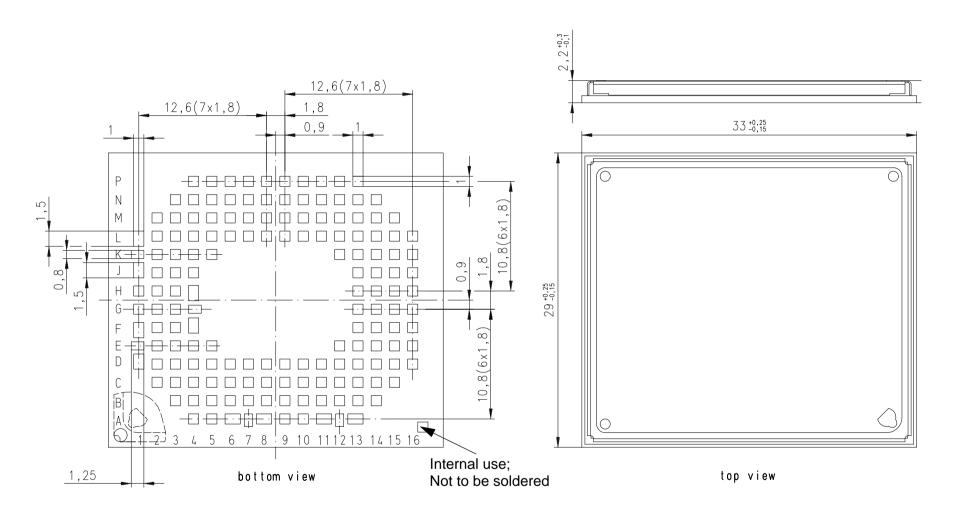


Figure 22: Dimensions of PLS8-E (all dimensions in mm)

#### 6.2 Mounting PLS8-E onto the Application Platform

This section describes how to mount PLS8-E onto the PCBs (=printed circuit boards), including land pattern and stencil design, board-level characterization, soldering conditions, durability and mechanical handling. For more information on issues related to SMT module integration see also [3].

Note: All SMT module pads need to be soldered to the application's PCB. Not only must all supply pads and signals be connected appropriately, but all pads denoted as "Do not use" will also have to be soldered (but not electrically connected) in order to ensure the best possible mechanical stability.

#### 6.2.1 SMT PCB Assembly

#### 6.2.1.1 Land Pattern and Stencil

The land pattern and stencil design as shown below is based on Cinterion characterizations for lead-free solder paste on a four-layer test PCB and a 110 respectively 150 micron-thick stencil.

The land pattern given in Figure 23 reflects the module's pad layout, including signal pads and ground pads (for pad assignment see Section 5.5). Besides these pads there are ground areas on the module's bottom side that must not be soldered, e.g., the position marker. To prevent short circuits, it has to be ensured that there are no wires on the external application side that may connect to these module ground areas.

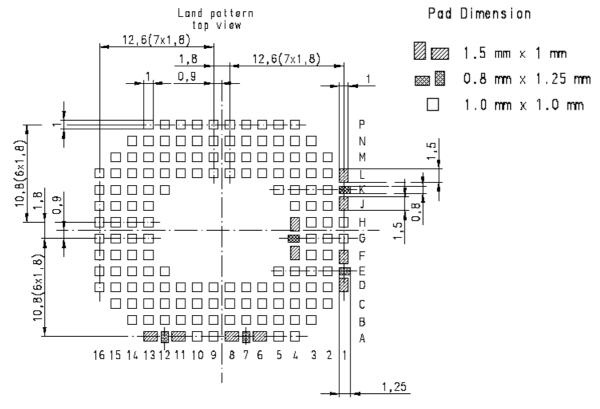


Figure 23: Land pattern (top layer)

The stencil design illustrated in Figure 24 and Figure 25 is recommended by Cinterion as a result of extensive tests with Cinterion Daisy Chain modules.

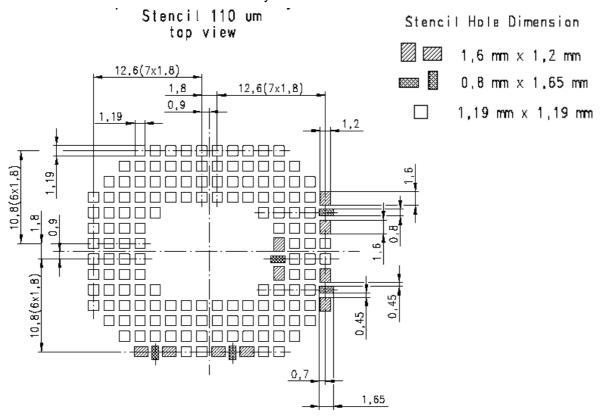


Figure 24: Recommended design for 110 micron thick stencil (top layer)

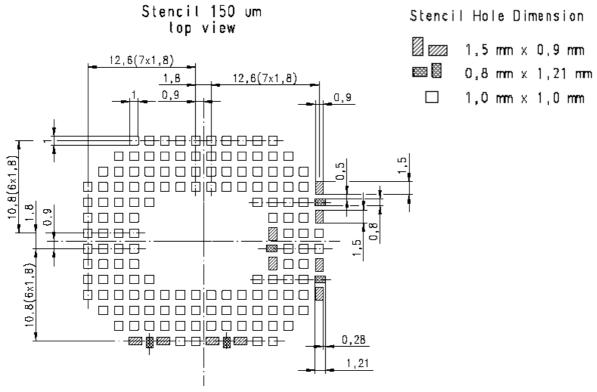


Figure 25: Recommended design for 150 micron thick stencil (top layer)

#### 6.2.1.2 Board Level Characterization

Board level characterization issues should also be taken into account if devising an SMT process.

Characterization tests should attempt to optimize the SMT process with regard to board level reliability. This can be done by performing the following physical tests on sample boards: Peel test, bend test, tensile pull test, drop shock test and temperature cycling. Sample surface mount checks are described in [3].

It is recommended to characterize land patterns before an actual PCB production, taking individual processes, materials, equipment, stencil design, and reflow profile into account. For land and stencil pattern design recommendations see also Section 6.2.1.1. Optimizing the solder stencil pattern design and print process is necessary to ensure print uniformity, to decrease solder voids, and to increase board level reliability.

Daisy chain modules for SMT characterization are available on request. For details refer to [3].

Generally, solder paste manufacturer recommendations for screen printing process parameters and reflow profile conditions should be followed. Maximum ratings are described in Section 6.2.3.

#### 6.2.2 Moisture Sensitivity Level

PLS8-E comprises components that are susceptible to damage induced by absorbed moisture.

Cinterion's PLS8-E module complies with the latest revision of the IPC/JEDEC J-STD-020 Standard for moisture sensitive surface mount devices and is classified as MSL 4.

For additional MSL (=moisture sensitivity level) related information see Section 6.2.4 and Section 6.3.2.

## 6.2.3 Soldering Conditions and Temperature

### 6.2.3.1 Reflow Profile

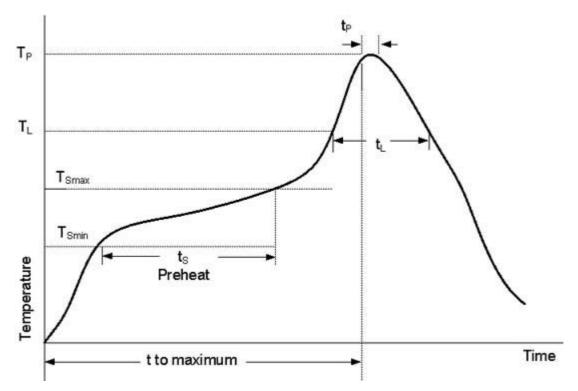


Figure 26: Reflow Profile

Table 22: Reflow temperature ratings

Profile Feature	Pb-Free Assembly
	150°C 200°C 60-120 seconds
Average ramp up rate (T <sub>Smax</sub> to T <sub>P</sub> )	3K/second max.
Liquidous temperature (T <sub>L</sub> ) Time at liquidous (t <sub>L</sub> )	217°C 60-90 seconds
Peak package body temperature (T <sub>P</sub> )	245°C +0/-5°C
Time $(t_P)$ within 5 °C of the peak package body temperature $(T_P)$	30 seconds max.
Average ramp-down rate (T <sub>P</sub> to T <sub>Smax</sub> )	6 K/second max.
Time 25°C to maximum temperature	8 minutes max.

### **6.2.3.2 Maximum Temperature and Duration**

The following limits are recommended for the SMT board-level soldering process to attach the module:

- A maximum module temperature of 245°C. This specifies the temperature as measured at the module's top side.
- A maximum duration of 30 seconds at this temperature.

Please note that while the solder paste manufacturers' recommendations for best temperature and duration for solder reflow should generally be followed, the limits listed above must not be exceeded.

PLS8-E is specified for one soldering cycle only. Once PLS8-E is removed from the application, the module will very likely be destroyed and cannot be soldered onto another application.

#### 6.2.4 Durability and Mechanical Handling

#### 6.2.4.1 Storage Life

PLS8-E modules, as delivered in tape and reel carriers, must be stored in sealed, moisture barrier anti-static bags. The shelf life in a sealed moisture bag is an estimated 12 month. However, such a life span requires a non-condensing atmospheric environment, ambient temperatures below 40°C and a relative humidity below 90%. Additional storage conditions are listed in Table 17.

#### 6.2.4.2 Processing Life

PLS8-E must be soldered to an application within 72 hours after opening the MBB (=moisture barrier bag) it was stored in.

As specified in the IPC/JEDEC J-STD-033 Standard, the manufacturing site processing the modules should have ambient temperatures below 30°C and a relative humidity below 60%.

#### **6.2.4.3** Baking

Baking conditions are specified on the moisture sensitivity label attached to each MBB (see Figure 31 for details):

- It is *not necessary* to bake PLS8-E, if the conditions specified in Section 6.2.4.1 and Section 6.2.4.2 were not exceeded.
- It is *necessary* to bake PLS8-E, if any condition specified in Section 6.2.4.1 and Section 6.2.4.2 was exceeded.

If baking is necessary, the modules must be put into trays that can be baked to at least 125°C. Devices should not be baked in tape and reel carriers at any temperature.

## **6.2.4.4** Electrostatic Discharge

ESD (=electrostatic discharge) may lead to irreversible damage for the module. It is therefore advisable to develop measures and methods to counter ESD and to use these to control the electrostatic environment at manufacturing sites.

Please refer to Section 5.8 for further information on electrostatic discharge.

### 6.3 Packaging

#### 6.3.1 Tape and Reel

The single-feed tape carrier for PLS8-E is illustrated in Figure 27. The figure also shows the proper part orientation. The tape width is 44mm and the PLS8-E modules are placed on the tape with a 40mm pitch. The reels are 330mm in diameter with 100mm hubs. Each reel contains 500 modules.

#### 6.3.1.1 Orientation

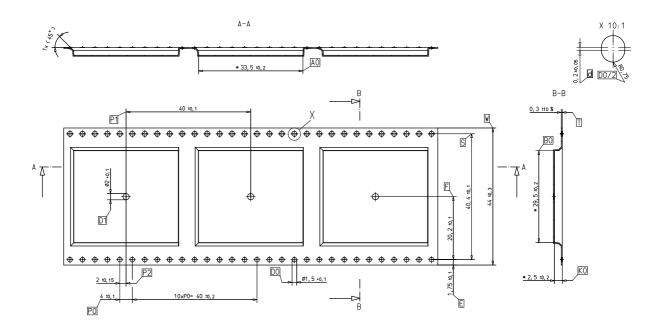


Figure 27: Carrier tape

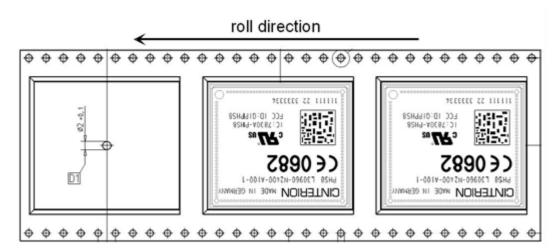


Figure 28: Roll direction

## 6.3.1.2 Barcode Label

A barcode label provides detailed information on the tape and its contents. It is attached to the reel.

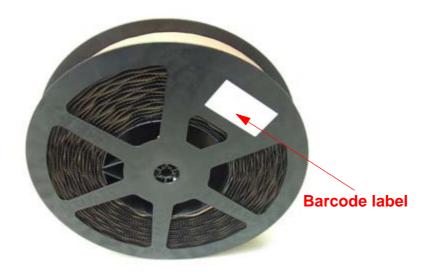


Figure 29: Barcode label on tape reel

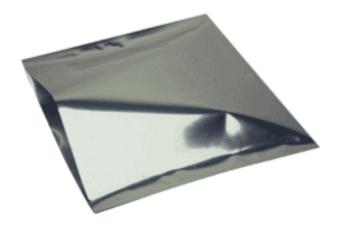
### 6.3.2 Shipping Materials

PLS8-E is distributed in tape and reel carriers. The tape and reel carriers used to distribute PLS8-E are packed as described below, including the following required shipping materials:

- Moisture barrier bag, including desiccant and humidity indicator card
- Transportation bag

#### 6.3.2.1 Moisture Barrier Bag

The tape reels are stored inside an MBB (=moisture barrier bag), together with a humidity indicator card and desiccant pouches - see Figure 30. The bag is ESD protected and delimits moisture transmission. It is vacuum-sealed and should be handled carefully to avoid puncturing or tearing. The bag protects the PLS8-E modules from moisture exposure. It should not be opened until the devices are ready to be soldered onto the application.



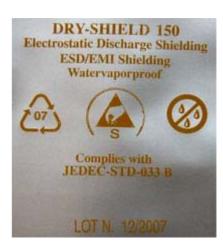


Figure 30: Moisture barrier bag (MBB) with imprint

The label shown in Figure 31 summarizes requirements regarding moisture sensitivity, including shelf life and baking requirements. It is attached to the outside of the moisture barrier bag.



Figure 31: Moisture Sensitivity Label

MBBs contain one or more desiccant pouches to absorb moisture that may be in the bag. The humidity indicator card described below should be used to determine whether the enclosed components have absorbed an excessive amount of moisture.

The desiccant pouches should not be baked or reused once removed from the MBB.

The humidity indicator card is a moisture indicator and is included in the MBB to show the approximate relative humidity level within the bag. Sample humidity cards are shown in Figure 32. If the components have been exposed to moisture above the recommended limits, the units will have to be rebaked.

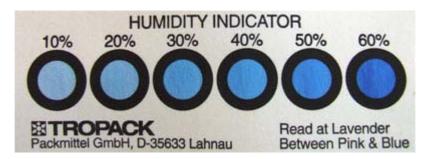


Figure 32: Humidity Indicator Card - HIC

A baking is required if the humidity indicator inside the bag indicates 10% RH or more.

#### 6.3.2.2 Transportation Box

Tape and reel carriers are distributed in a box, marked with a barcode label for identification purposes. A box contains 2 reels with 500 modules each.

### 7 Sample Application

Figure 33 shows a typical example of how to integrate an PLS8-E module with an application.

The PWR\_IND line is an open collector that needs an external pull-up resistor which connects to the voltage supply VCC  $\mu$ C of the microcontroller. Low state of the open collector pulls the PWR\_IND signal low and indicates that the PLS8-E module is active, high level notifies the Power-down mode.

If the module is in Power-down mode avoid current flowing from any other source into the module circuit, for example reverse current from high state external control lines. Therefore, the controlling application must be designed to prevent reverse flow.

While developing SMT applications it is strongly recommended to provide test points for certain signals resp. lines to and from the module - for debug and/or test purposes. The SMT application should allow for an easy access to these signals. For details on how to implement test points see [3].

The EMC measures are best practice recommendations. In fact, an adequate EMC strategy for an individual application is very much determined by the overall layout and, especially, the position of components.

Some LGA pads are connected to clocks or high speed data streams that might interfere with the module's antenna. The RF receiver would then be blocked at certain frequencies (self interference). The external application's PCB tracks connected to these pads should therefore be well shielded or kept away from the antenna. This applies especially to the USB and UICC/SIM interfaces.

#### Disclaimer:

No warranty, either stated or implied, is provided on the sample schematic diagram shown in Figure 33 and the information detailed in this section. As functionality and compliance with national regulations depend to a great amount on the used electronic components and the individual application layout manufacturers are required to ensure adequate design and operating safeguards for their products using PLS8-E modules.

# Sample Application

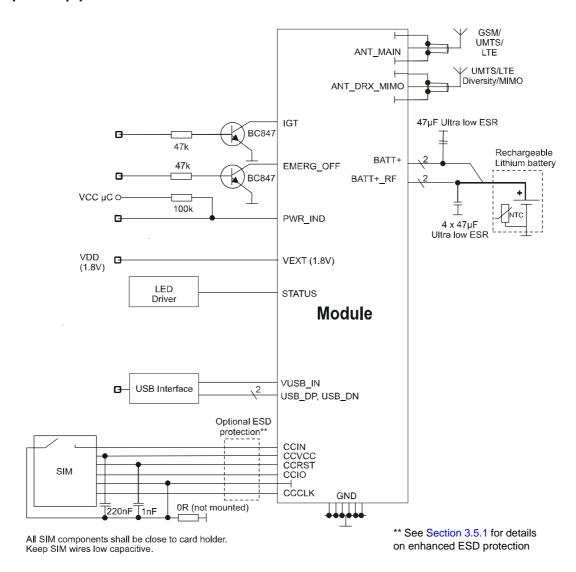


Figure 33: PLS8-E sample application

### 8 Reference Approval

#### 8.1 Reference Equipment for Type Approval

The Cinterion Wireless Modules reference setup submitted to type approve PLS8-E is shown in Figure 34. The module (i.e., the evaluation module) is connected to the DSB75 by means of a flex cable and a special DSB75 adapter. The GSM/UMTS/LTE test equipment is connected via edge mount SMA connectors soldered to the module's antenna pads.

For ESD tests and evaluation purposes, it is also possible connect the module to the GSM/ UMTS/LTE test equipment through an SMA-to-Hirose-U.FL antenna cable and the SMA antenna connectors of the DSB75 adapter.

A further option is to mount the evaluation module directly onto the DSB75 adapter's 80-pin board-to-board connector and to connect the test equipment as shown below.

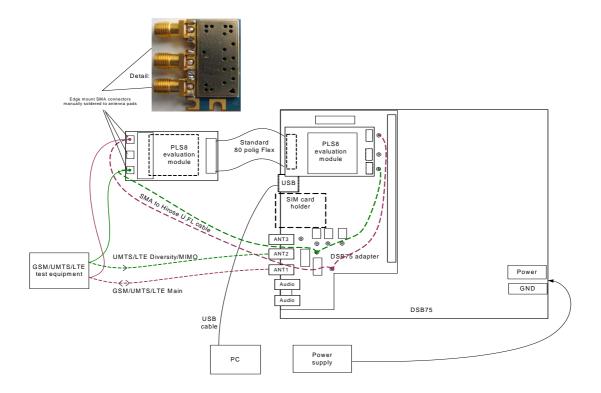


Figure 34: Reference equipment for type approval

# 9 Appendix

### 9.1 List of Parts and Accessories

Table 23: List of parts and accessories

Description	Supplier	Ordering information
PLS8-E	Cinterion	Standard module Cinterion Wireless Modules IMEI: Packaging unit (ordering) number: L30960-N3400-A100 Module label number: S30960-S3400-A100-1
PLS8-E Evaluation Module	Cinterion	Ordering number: L30960-N3401-A100
DSB75 Support Box	Cinterion	Ordering number: L36880-N8811-A100
DSB75 adapter for mounting the evaluation module	Cinterion	Ordering number: L30960-N2301-A100
SIM card holder incl. push button ejector and slide-in tray	Molex	Ordering numbers: 91228 91236 Sales contacts are listed in Table 24.
U.FL antenna connector	Hirose or Molex	Sales contacts are listed in Table 24 and Table 25.

Table 24: Molex sales contacts (subject to change)

Molex For further information please click: http://www.molex.com	Molex Deutschland GmbH Otto-Hahn-Str. 1b 69190 Walldorf Germany Phone: +49-6227-3091-0 Fax: +49-6227-3091-8100 Email: mxgermany@molex.com	American Headquarters Lisle, Illinois 60532 U.S.A. Phone: +1-800-78MOLEX Fax: +1-630-969-1352
Molex China Distributors Beijing, Room 1311, Tower B, COFCO Plaza No. 8, Jian Guo Men Nei Street, 100005 Beijing P.R. China Phone: +86-10-6526-9628 Fax: +86-10-6526-9730	Molex Singapore Pte. Ltd. 110, International Road Jurong Town, Singapore 629174 Phone: +65-6-268-6868 Fax: +65-6-265-6044	Molex Japan Co. Ltd. 1-5-4 Fukami-Higashi, Yamato-City, Kanagawa, 242-8585 Japan Phone: +81-46-265-2325 Fax: +81-46-265-2365

Table 25: Hirose sales contacts (subject to change)

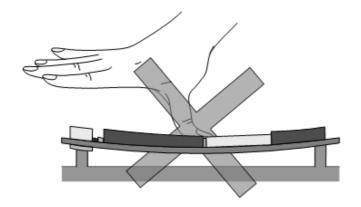
Hirose Ltd. For further information please click: http://www.hirose.com	Hirose Electric (U.S.A.) Inc 2688 Westhills Court Simi Valley, CA 93065 U.S.A. Phone: +1-805-522-7958 Fax: +1-805-522-3217	Hirose Electric Europe B.V. German Branch: Herzog-Carl-Strasse 4 73760 Ostfildern Germany Phone: +49-711-456002-1 Fax: +49-711-456002-299 Email: info@hirose.de
Hirose Electric Europe B.V. UK Branch: First Floor, St. Andrews House, Caldecotte Lake Business Park, Milton Keynes MK7 8LE Great Britain Phone: +44-1908-369060	Hirose Electric Co., Ltd. 5-23, Osaki 5 Chome, Shinagawa-Ku Tokyo 141 Japan Phone: +81-03-3491-9741	Hirose Electric Europe B.V. Hogehillweg 8 1101 CC Amsterdam Z-O Netherlands
Fax: +44-1908-369078	Fax: +81-03-3493-2933	Fax: +31-20-6557-469

### 9.2 Mounting Advice Sheet

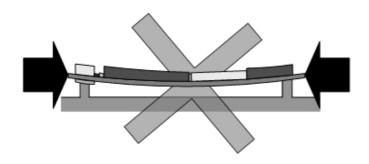
To prevent mechanical damage, be careful not to force, bend or twist the module. Be sure it is soldered flat against the host device (see also Section 6.2). The advice sheet on the next page shows a number of examples for the kind of bending that may lead to mechanical damage of the module (the module as part of an external application is integrated into a housing).

#### **Mounting Advice**

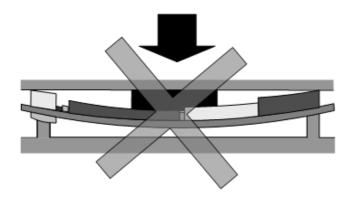
## Do NOT BEND the Module



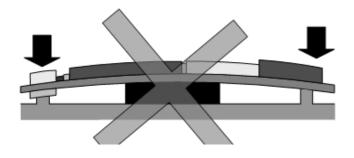
- By pressing from above



- By mounting under pressure



- By putting objects on top



- By putting objects below

#### **About Gemalto**

Gemalto (Euronext NL0000400653 GTO) is the world leader in digital security with 2011 annual revenues of €2 billion and more than 10,000 employees operating out of 74 offices and 14 Research & Development centers, located in 43 countries.

We are at the heart of the rapidly evolving digital society. Billions of people worldwide increasingly want the freedom to communicate, travel, shop, bank, entertain and work - anytime, everywhere - in ways that are enjoyable and safe. Gemalto delivers on their expanding needs for personal mobile services, payment security, authenticated cloud access, identity and privacy protection, eHealthcare and eGovernment efficiency, convenient ticketing and dependable machine-to-machine (M2M) applications.

Gemalto develops secure embedded software and secure products which we design and personalize. Our platforms and services manage these secure products, the confidential data they contain and the trusted end-user services they enable. Our inovations enable our clients to offer trusted and convenient digital services to billions of individuals.

Gemalto thrives with the growing number of people using its solutions to interact with the digital and wireless world.

#### For more information please visit

 $m2m.gemal to.com, www.facebook.com/gemal to, or Follow@gemal tom2m \ on \ twitter.$ 

**Gemalto M2M GmbH** 

St.-Martin-Str. 60 81541 Munich Germany

